

EE 435

# Lecture 41

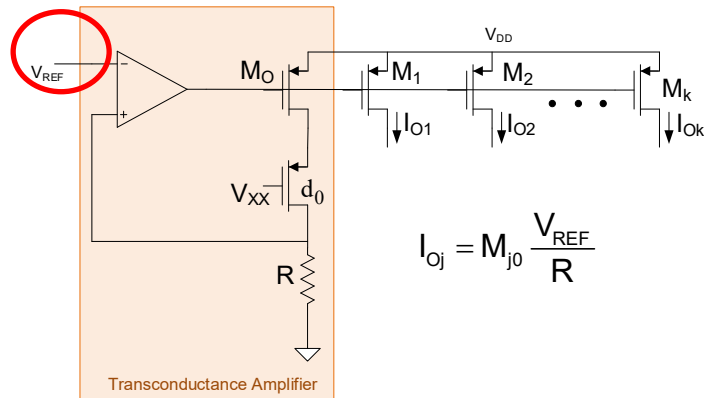
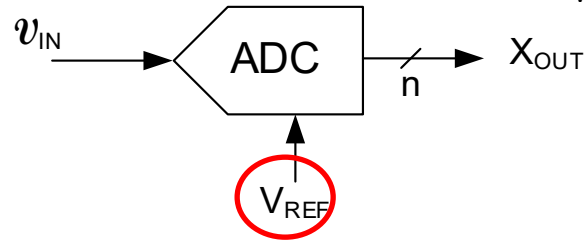
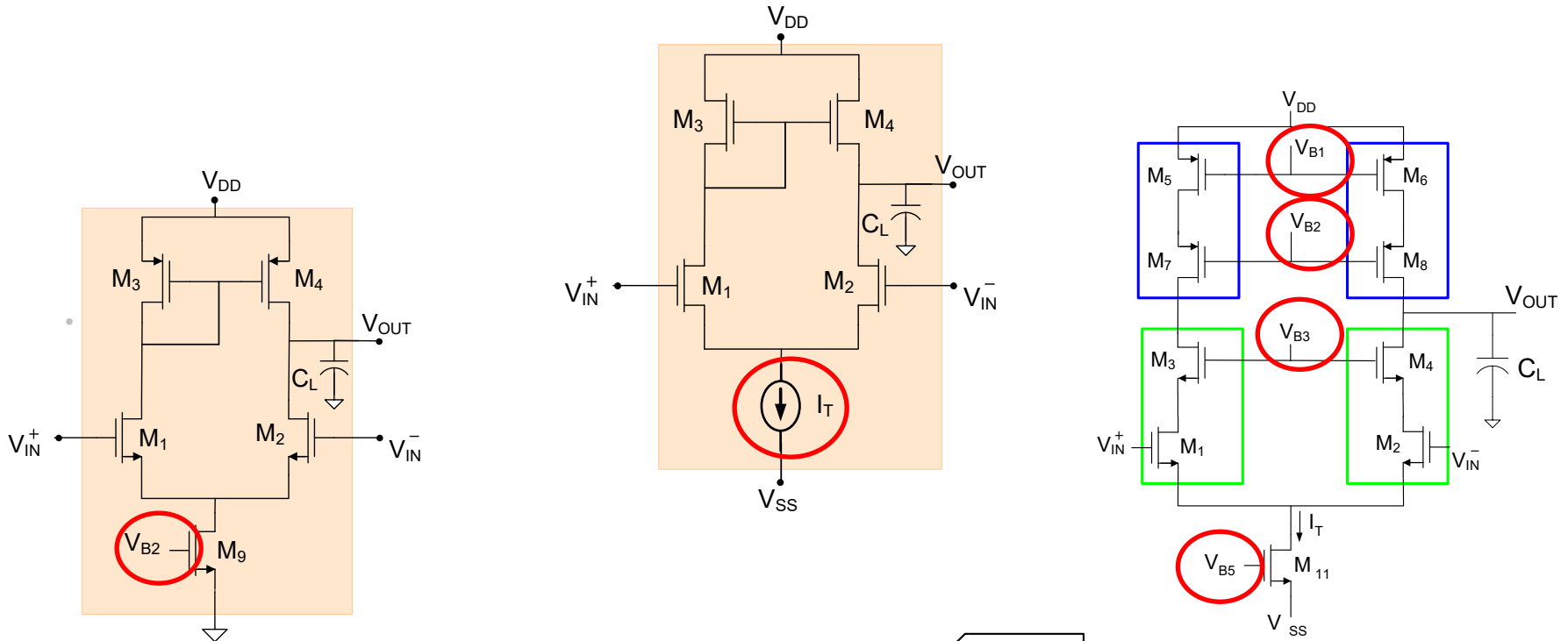
References and Bias Generators

# Bias Voltages/Currents and References

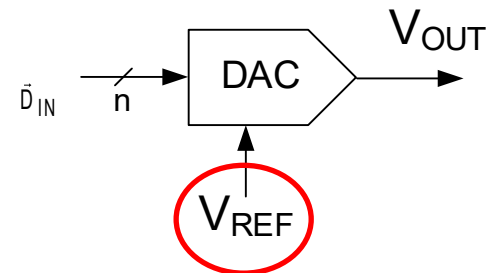
How do we get quantities such as voltage, current, resistance, temperature, ?.... in an electronic circuit

# Bias Voltages/Currents and References

How are these voltages and currents generated?

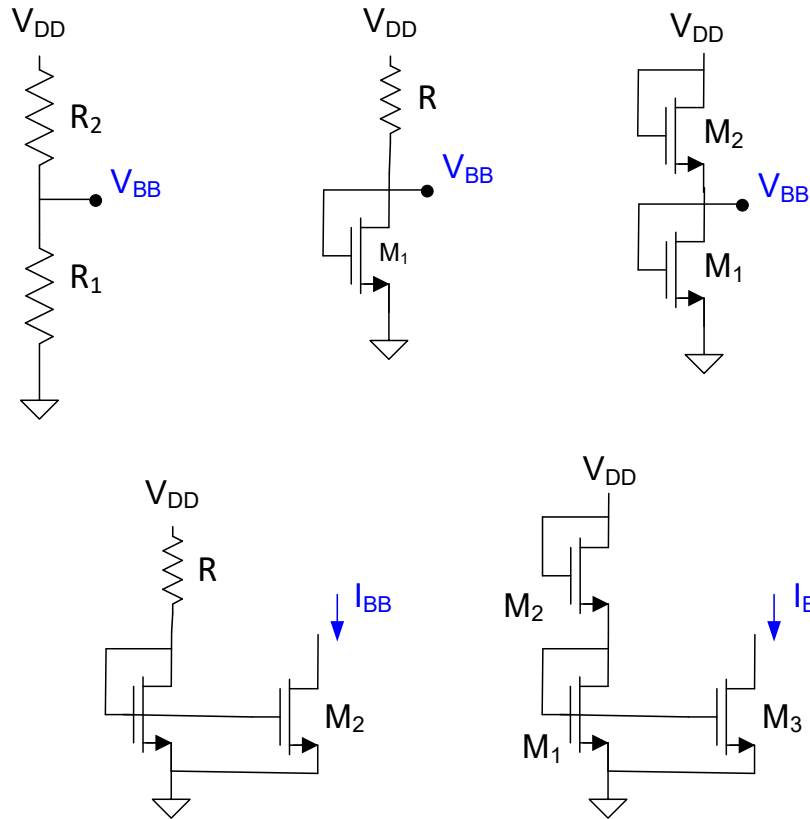


$$I_{Oj} = M_{j0} \frac{V_{REF}}{R}$$



# Bias Voltages/Currents and References

How are these voltages and currents generated?



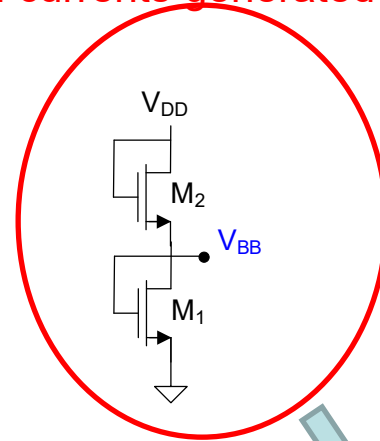
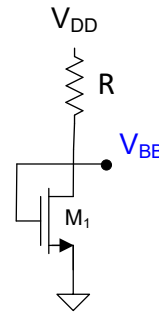
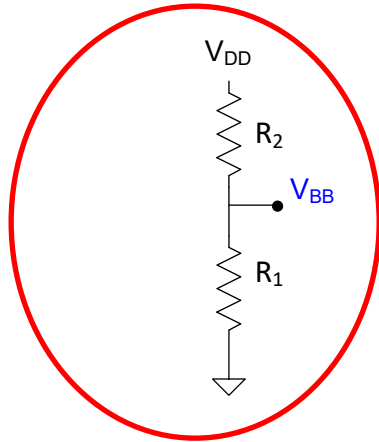
All will work !

Termed Supply-Referenced Sources

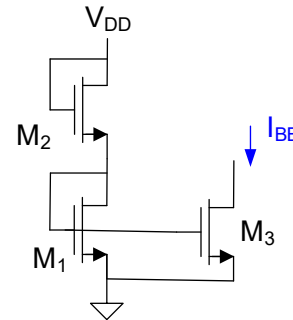
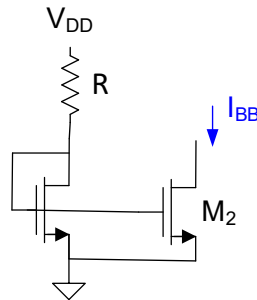
But supply sensitivity (supplies usually poorly controlled and noisy), process dependence, and temperature dependence unacceptable in many applications

# Bias Voltages/Currents and References

How are these voltages and currents generated?



$$V_{BB} = V_{DD} \left( \frac{R_1}{R_1 + R_2} \right)$$

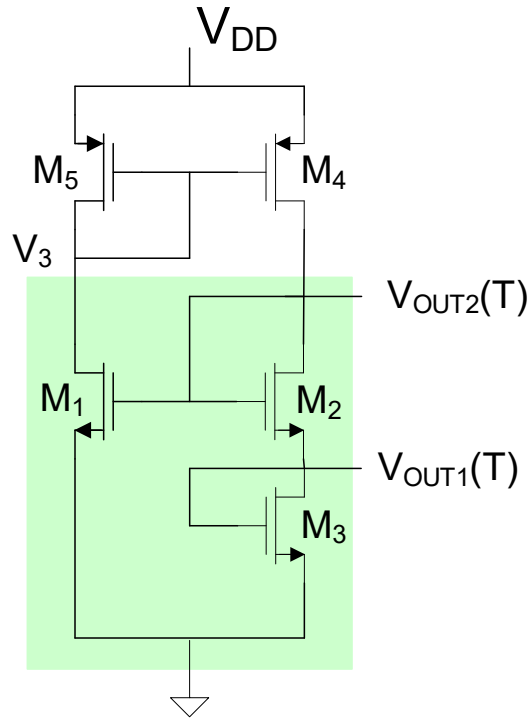


$$V_{BB} = V_{DD} \left( \frac{\sqrt{\frac{W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}} \right) + V_{TH} \left( \frac{1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}} \right)$$

For voltage references, must find circuit that generates output that has units Volts !  
 For current references, must find circuit that generates output that has units Amps !

# Bias Voltages/Currents Generators

How are these voltages and currents generated?



Inverse-Widlar

$$V_{O1} = V_{Tn} \left( \frac{1 - \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{W_2 L_3}{W_3 L_2}} - \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}} \right)$$

$$V_{O2} = V_{Tn} \left( \frac{1 + \sqrt{\frac{W_2 L_3}{W_3 L_2}} - 2 \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}}{1 + \sqrt{\frac{W_2 L_3}{W_3 L_2}} - \sqrt{\frac{M_{54} W_2 L_1}{W_1 L_2}}} \right)$$

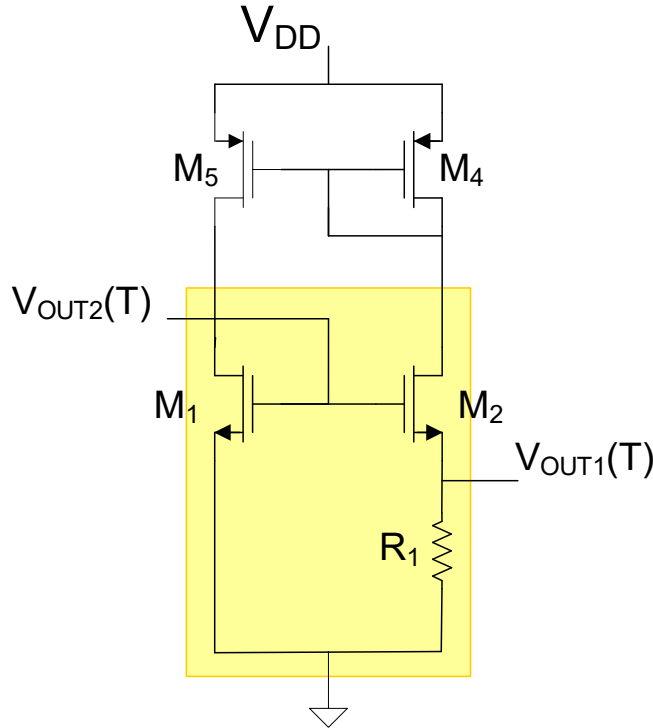
$M_{54}$  is the  $M_5:M_4$  Current Mirror Gain

Supply-independent Bias Generator!

Start-up circuit needed (notice positive feedback loop)

Supply-independent Bias Generators Widely Used

# Bias Voltages/Currents Generators



$$V_{O1} = \left( \frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left( \frac{\theta_1}{2} \right)^2} \right) \left( 1 - \sqrt{\frac{W_1 L_2}{M_{45} W_2 L_1}} \right)$$

$$V_{O2} = V_{Tn} + \frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left( \frac{\theta_1}{2} \right)^2}$$

where

$$\theta_1 = \frac{M_{45} 2L_1}{R \mu_n C_{OX} W_1}$$

Widlar Generator !

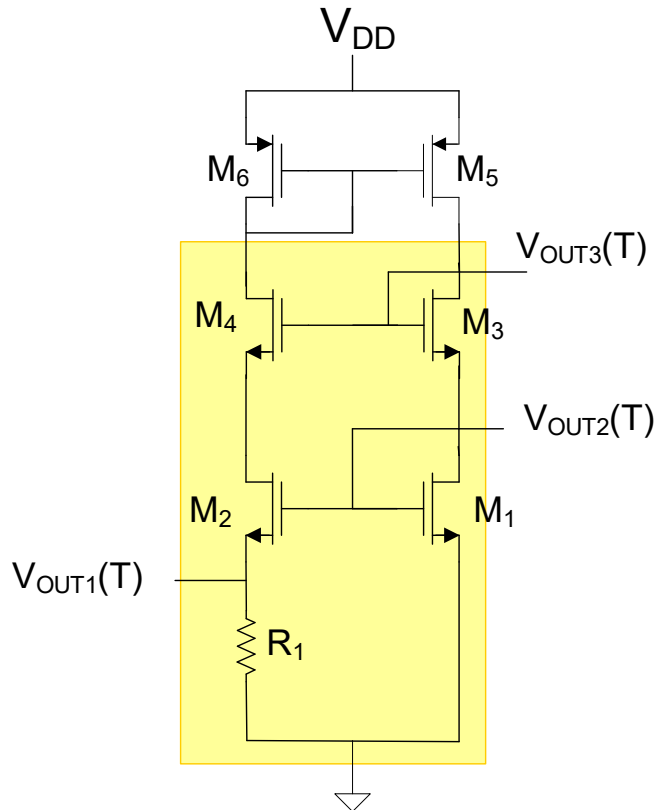
$M_{45}$  is the  $M_4:M_5$  Current Mirror Gain

Supply-independent Bias Generator!

Start-up circuit needed (notice positive feedback loop)

Supply-independent Bias Generators Widely Used

# Bias Voltages/Currents Generators



Martin Johns Page 307

$$V_{01} = \left( \frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left( \frac{\theta_1}{2} \right)^2} \right) \left( 1 - \sqrt{\frac{W_1 L_2}{M_{65} W_2 L_1}} \right)$$

$$V_{02} = V_{Tn} + \frac{\theta_1}{2} \pm \sqrt{\frac{\theta_1 V_{Tn}}{2} + \left( \frac{\theta_1}{2} \right)^2}$$

where

$$\theta_1 = \frac{M_{65} 2L_1}{R \mu_n C_{OX} W_1}$$

M<sub>65</sub> is the M<sub>6</sub>:M<sub>5</sub> Current Mirror Gain

**Widlar Generator !**

Supply-independent Bias Generator!

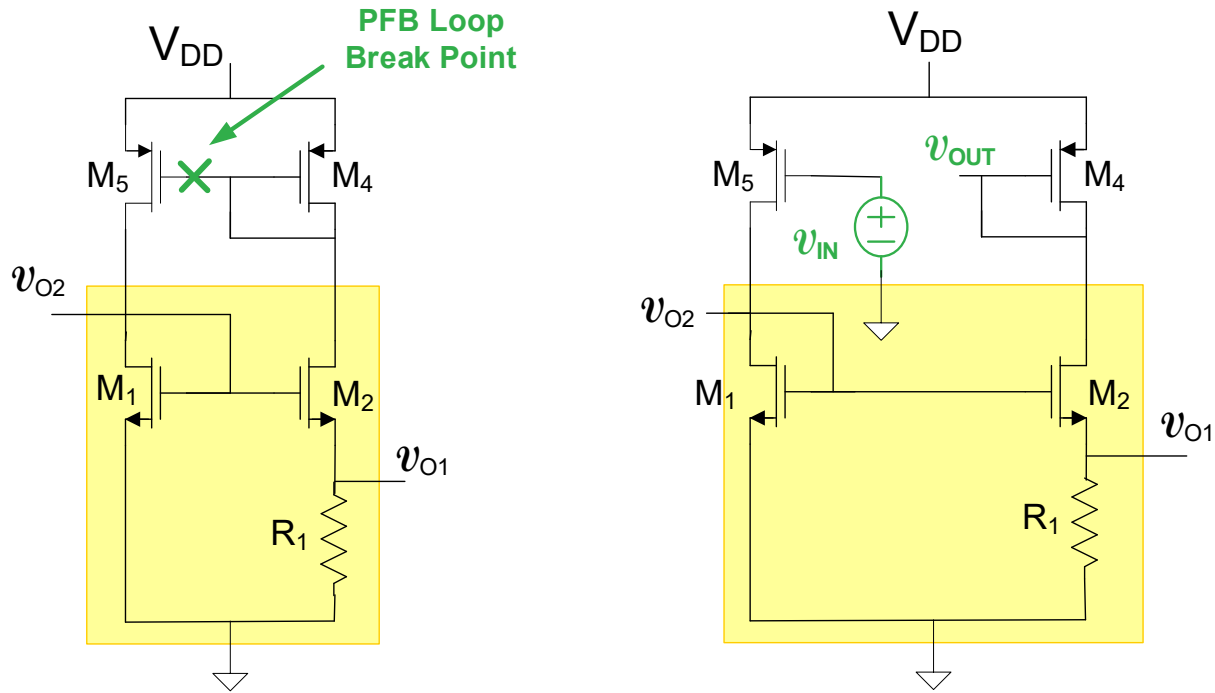
Start-up circuit needed (notice positive feedback loop)

Supply-independent Bias Generators Widely Used



# Bias Voltages/Currents Generators

Need for Start-up Circuit



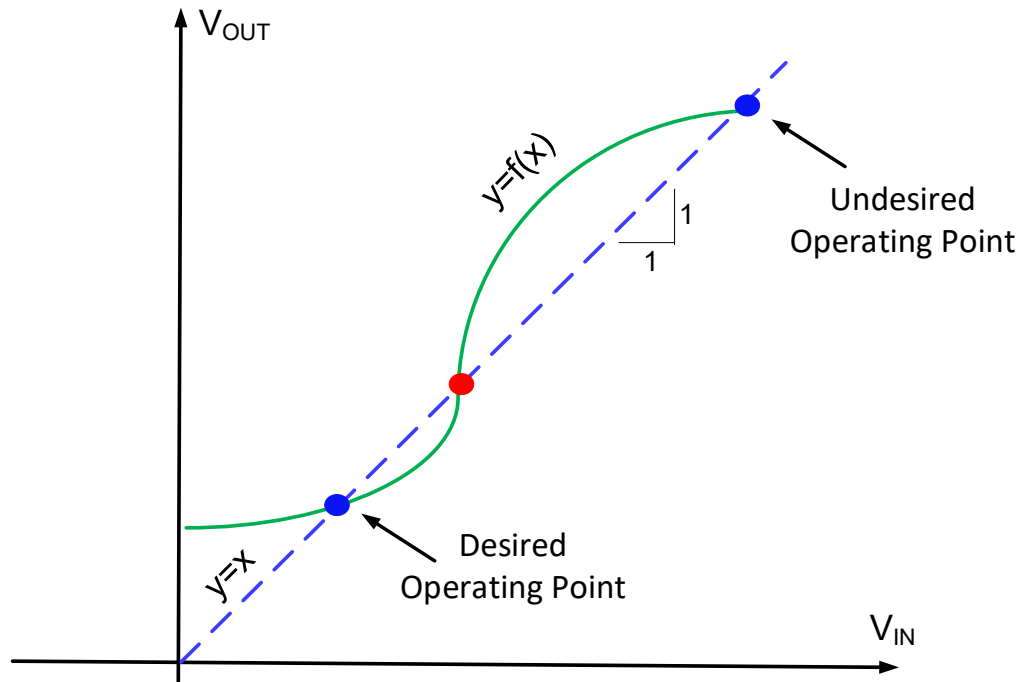
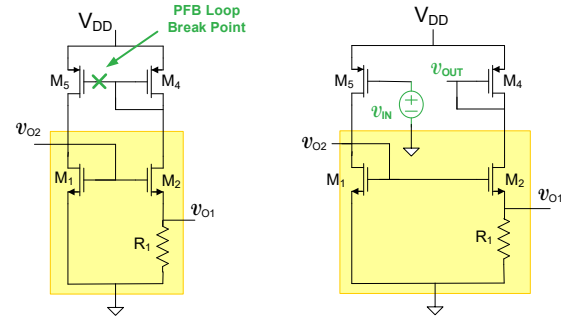
$V_{OUT}=f(V_{IN})$  termed the return map

Termed Homotopy Analysis

Must not perturb operating point when breaking loop !

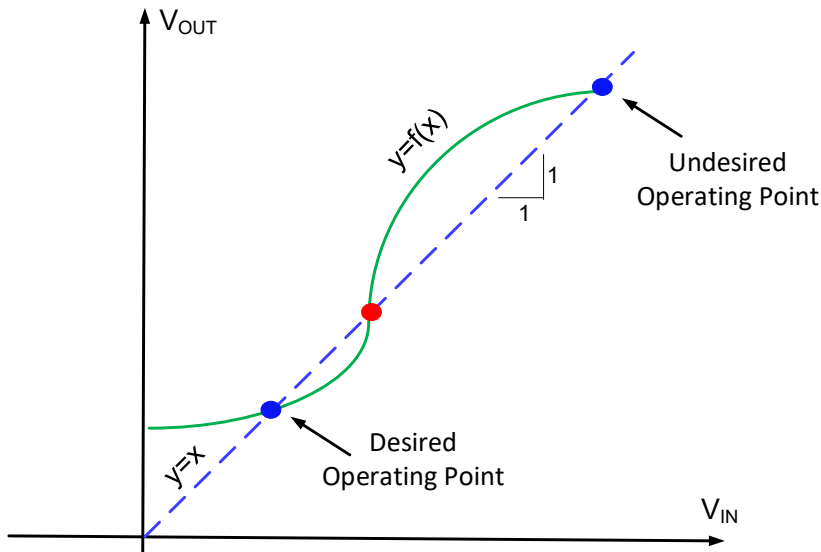
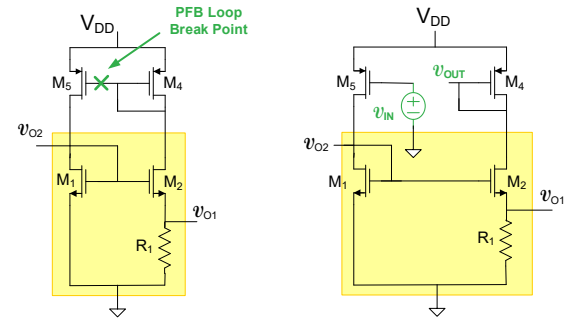
# Bias Voltages/Currents Generators

Need for Start-up Circuit

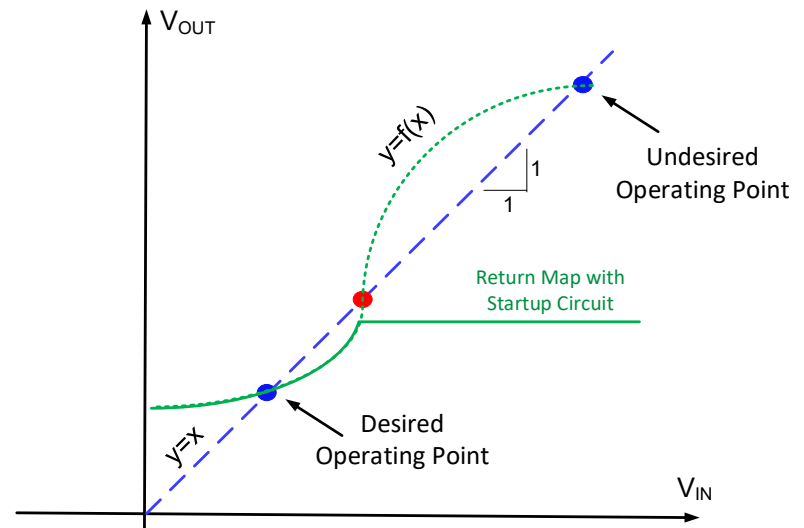


# Bias Voltages/Currents Generators

Need for Start-up Circuit



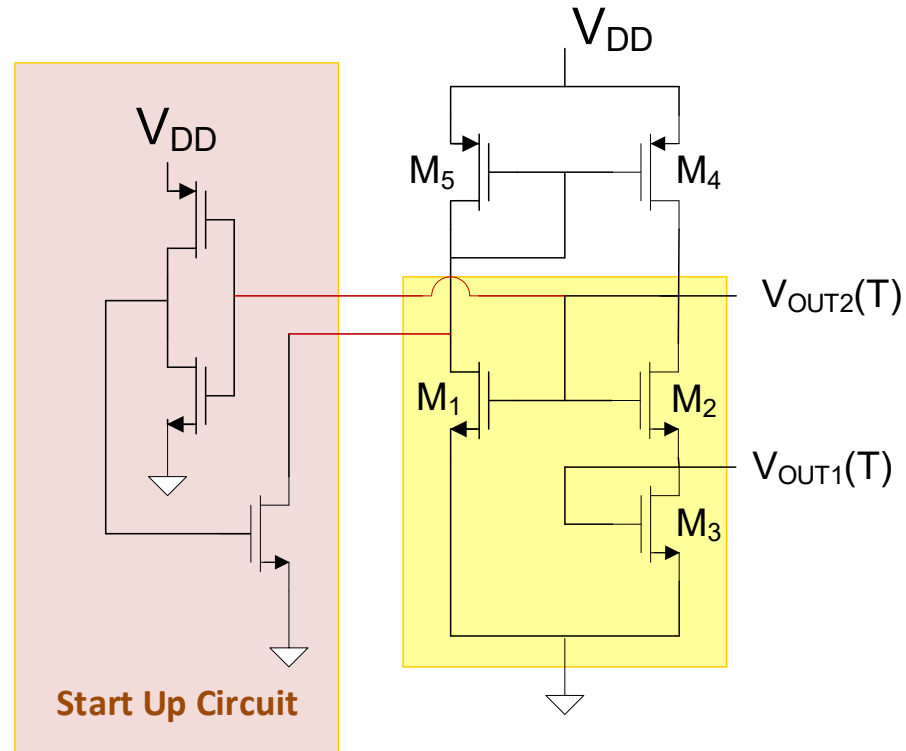
Without start-up circuit



With start-up circuit

Must verify start-up is effective over PVT variations

# Bias Voltages/Currents Generators



Several different start-up circuits have been used

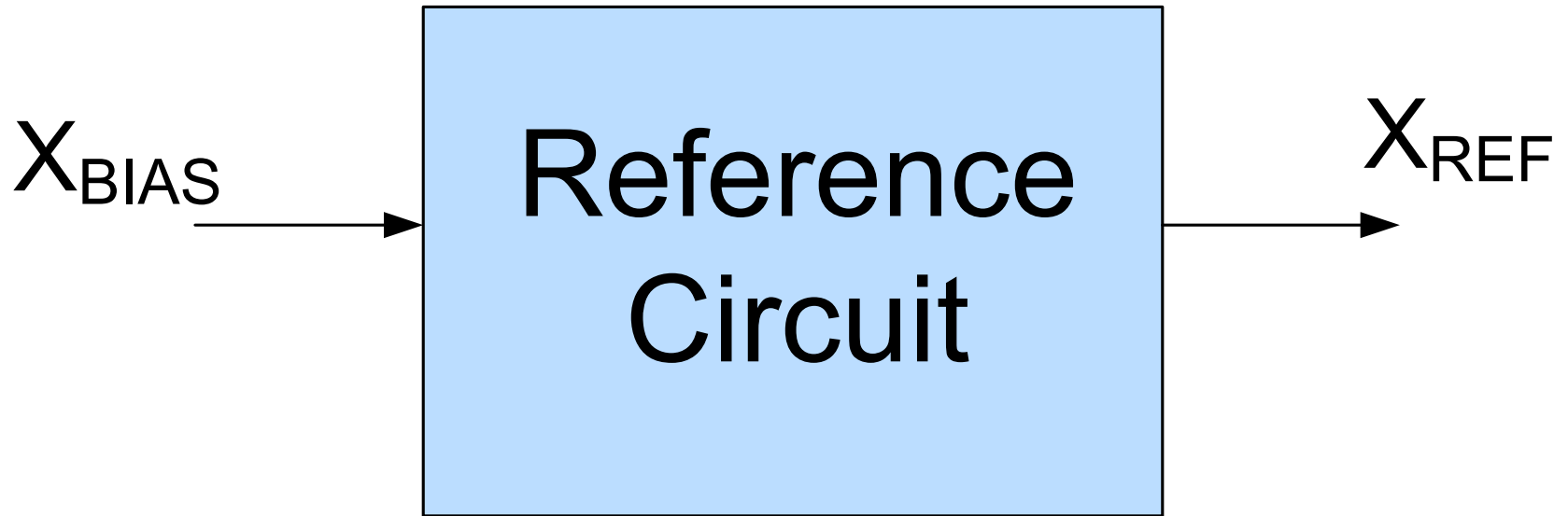
This start-up circuit shuts off during normal operation !

# Types of References

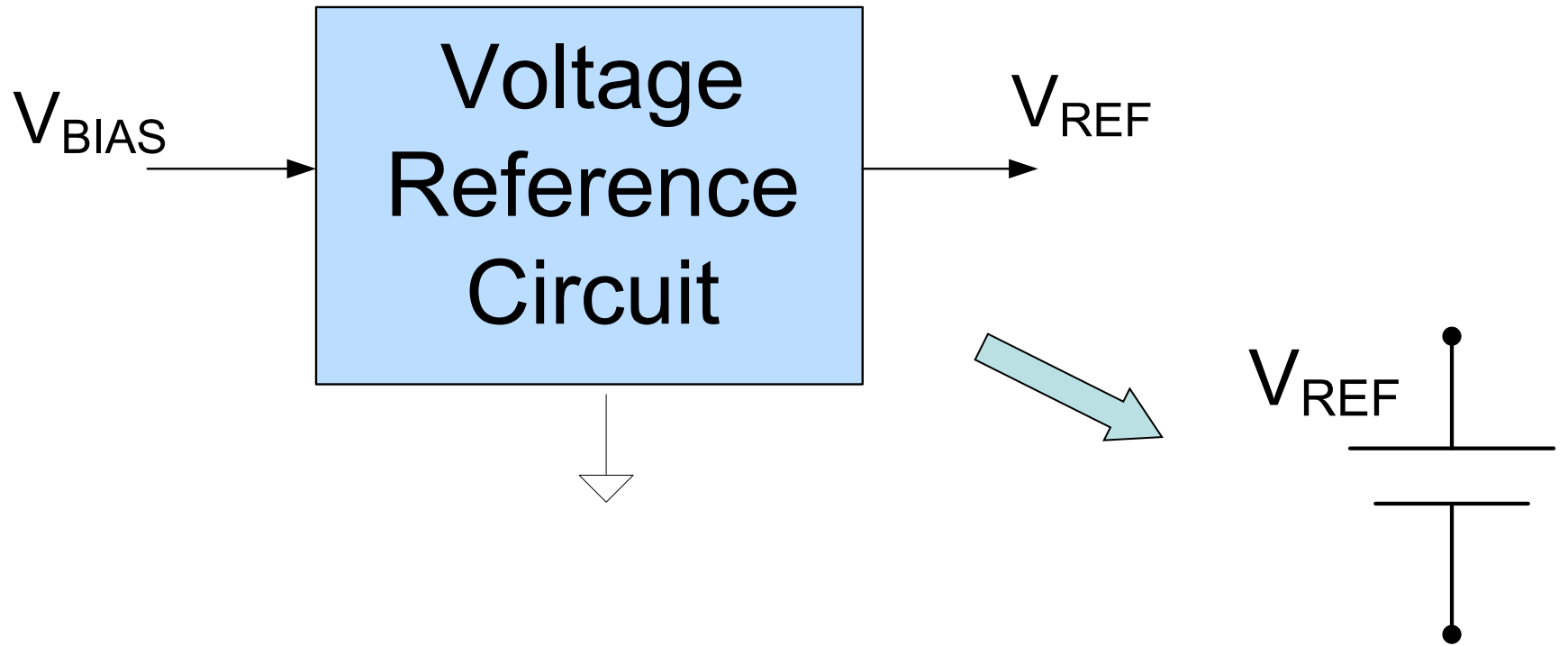
- Voltage References
- Current References
- Time References
- .....

## Sensors Closely Related

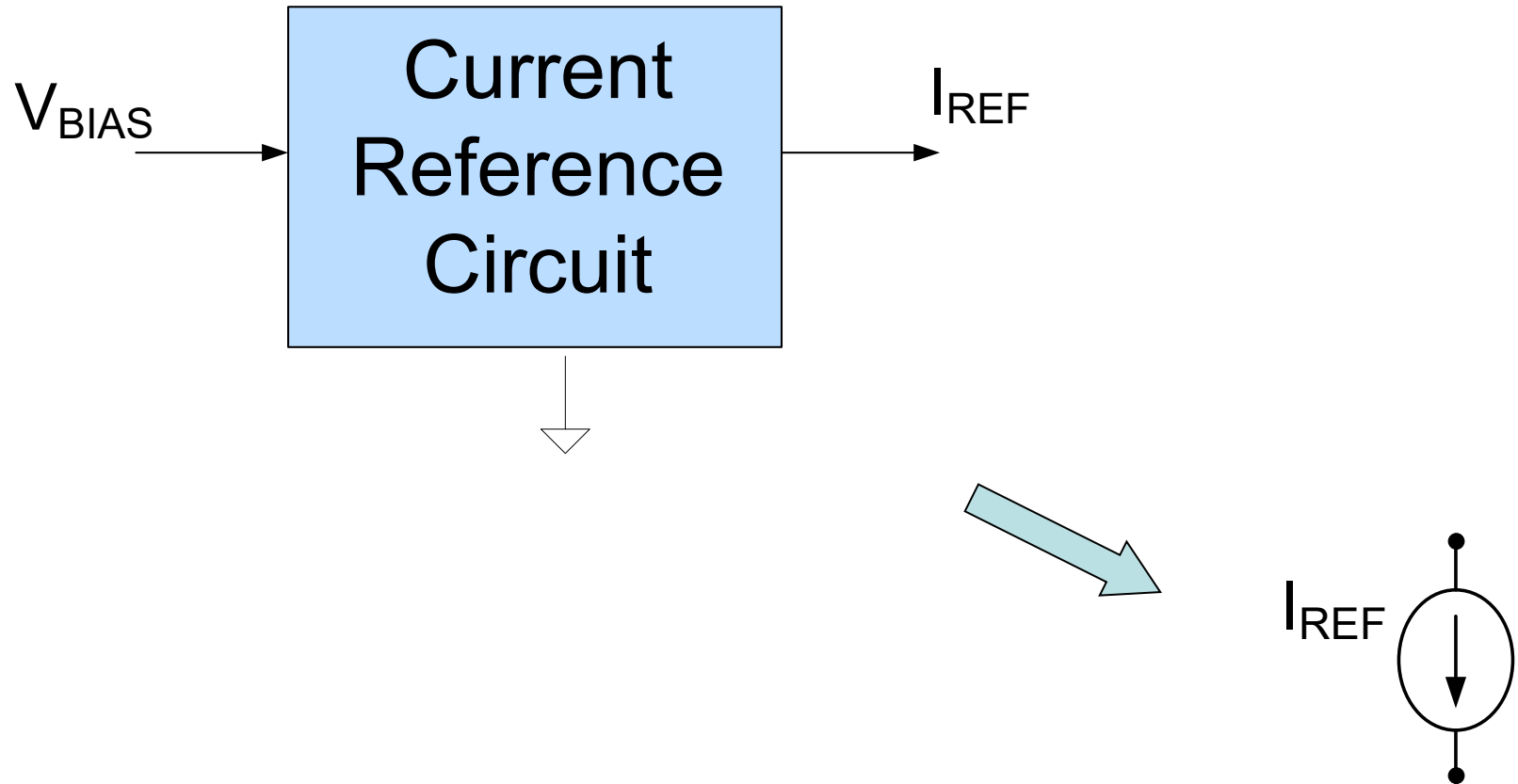
- Temperature
- Period
- Resistance
- Capacitance
- .....



# Voltage Reference

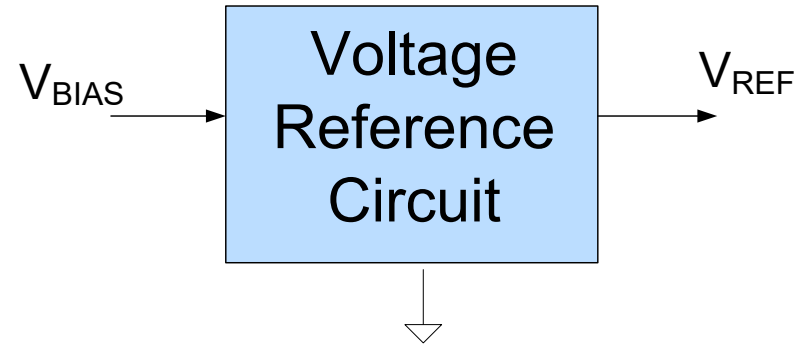


# Current Reference



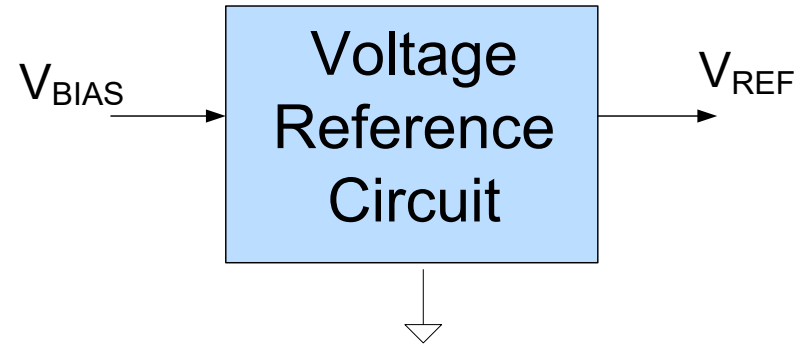


# Desired Properties of References



- Accurate
- Temperature Stable
- Time Stable
- Insensitive to  $V_{\text{BIAS}}$
- Low Output Impedance (voltage reference)
- Floating
- Small Area
- Low Power Dissipation
- Process Tolerant
- Process Transportable

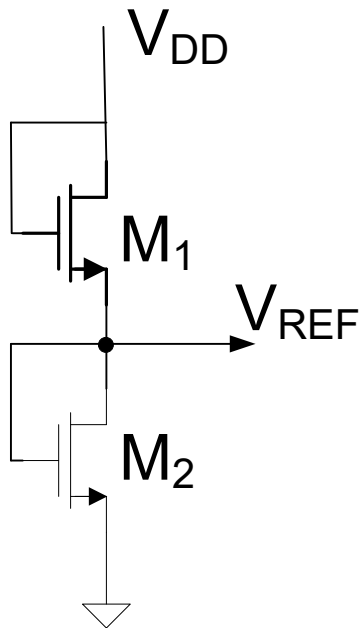
# Desired Properties of References



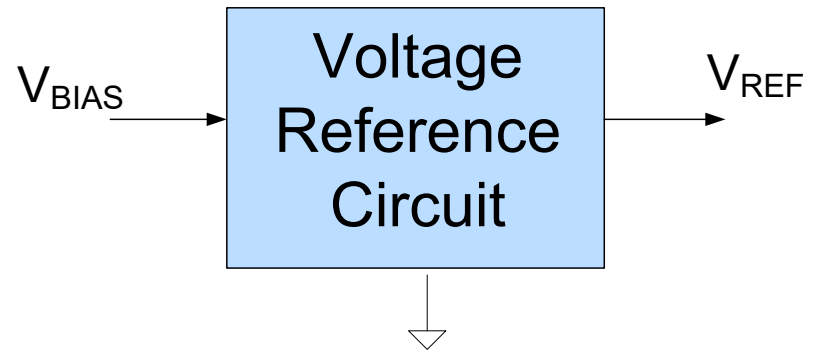
- Accurate ✓
- Temperature Stable ✓
- Time Stable ✓
- Insensitive to  $V_{BIAS}$  ✓
- Low Output Impedance (voltage reference)
- Floating
- Small Area
- Low Power Dissipation
- Process Tolerant ✓
- Process Transportable

Similar properties desired in other references

# Consider Voltage References



Popular Voltage “Reference”

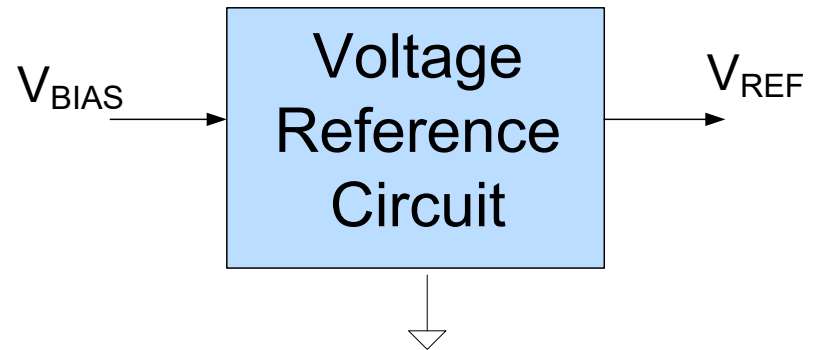


$$\left. \begin{aligned}
 I_{D1} &= \frac{\mu C_{OX} W_1}{2L_1} (V_{GS1} - V_{T1})^2 \\
 I_{D2} &= \frac{\mu C_{OX} W_2}{2L_2} (V_{GS2} - V_{T2})^2 \\
 V_{T1} &= V_{TH0} + \gamma \left( \sqrt{\phi + V_{REF}} - \sqrt{\phi} \right) \\
 V_{DD} - V_{REF} - V_{T1} &= \sqrt{\frac{W_2 L_1}{W_1 L_2}} (V_{REF} - V_{T2})
 \end{aligned} \right\}$$

If matching assumed and  $\gamma$  effects neglected

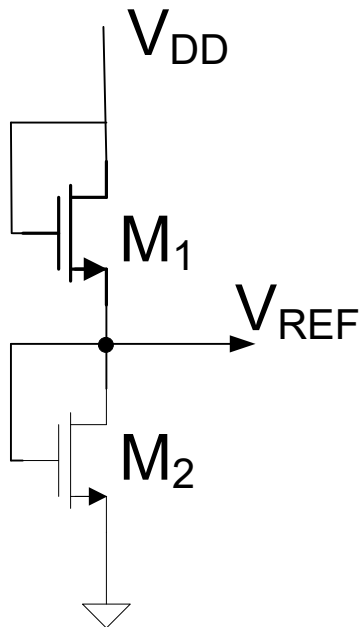
$$V_{REF} = \frac{V_{DD} - V_{TH0} \left( 1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}} \right)}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}}$$

# Consider Voltage References



If matching assumed and  $\gamma$  effects neglected

$$V_{REF} = \frac{V_{DD} - V_{TH0} \left( 1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}} \right)}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}}$$



Popular Voltage “Reference”

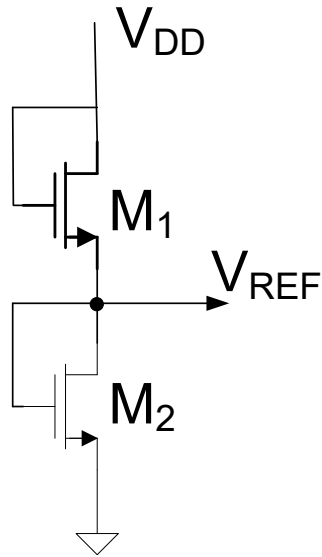
Uses as a reference limited to biasing and even for this may not be good enough !

Dependent upon  $V_{DD}$ ,  $V_{TH0}$ , matching, process variations,  $\gamma$

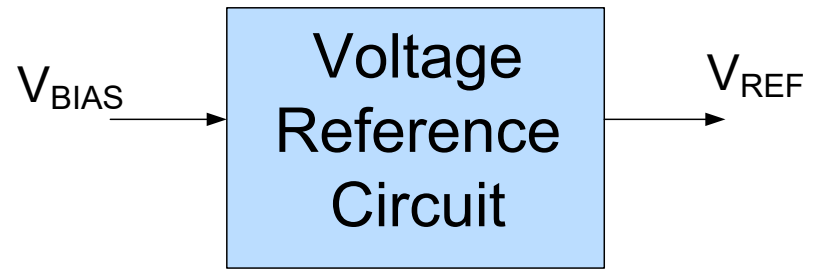
Termed a  $V_{DD}, V_{TH}$  reference

Does not satisfy key properties of voltage references

# Consider Voltage References



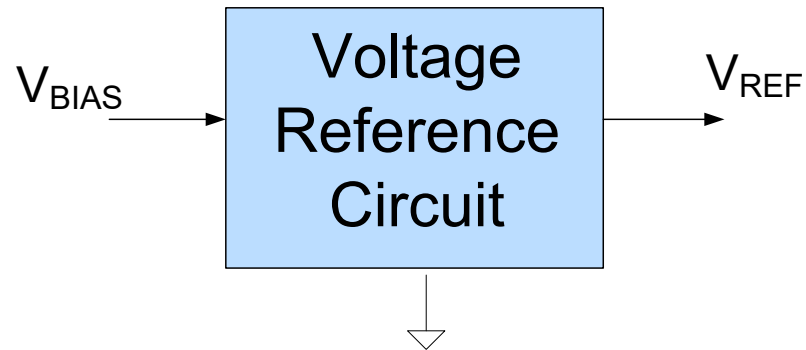
$V_{DD}, V_T$  reference



$$V_{REF} = \frac{V_{DD} - V_{T0} \left( 1 - \sqrt{\frac{W_2 L_1}{W_1 L_2}} \right)}{1 + \sqrt{\frac{W_2 L_1}{W_1 L_2}}}$$

Observation – Variables with units Volts needed to build any voltage reference

# Voltage References



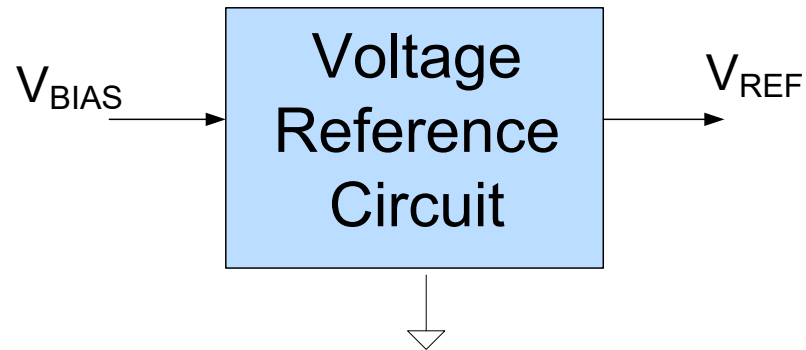
Observation – Variables with units Volts needed to build any voltage reference

What variables available in a process have units volts?

What variables which have units volts satisfy the desired properties of a voltage reference?

How can a circuit be designed that “expresses” the desired variables?

# Voltage References



Observation – Variables with units Volts needed to build any voltage reference

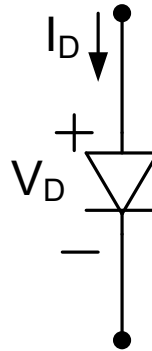
What variables available in a process have units volts?

$V_{DD}$ ,  $V_T$ ,  $V_D$  (diode),  $V_Z$ ,  $V_{BE}$ ,  $V_t$ ,  $V_{TH}$  ???

What variables which have units volts satisfy the desired properties of a voltage reference?

How can a circuit be designed that “expresses” the desired variables?

# Voltage References



Consider the Diode

$$I_D = J_S A e^{\frac{V_D}{V_t}}$$

$$V_t = \frac{kT}{q}$$
$$\frac{k}{q} = \frac{1.38 \times 10^{-23} \text{ V}}{1.602 \times 10^{-19}} = 8.614 \times 10^{-5} \frac{\text{V}}{^\circ\text{K}}$$

$$J_S = \tilde{J}_{SX} \left[ T^m e^{\frac{-V_{G0}}{V_t}} \right]$$

$$V_{G0} = 1.206\text{V}$$

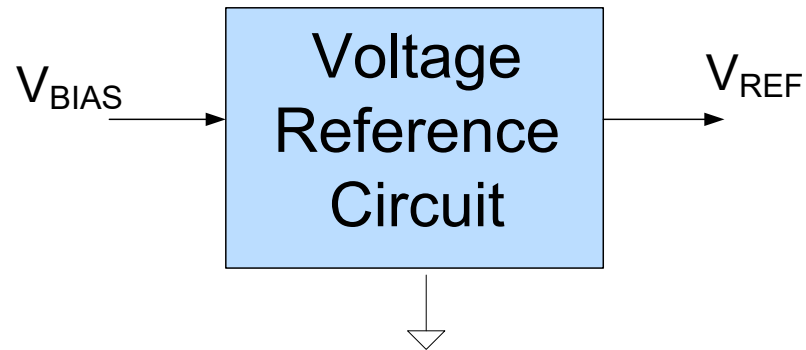
termed the bandgap voltage

pn junction characteristics highly temperature dependent through both the exponent and  $J_S$

$V_{G0}$  is nearly independent of process and temperature



# Voltage References



Observation – Variables with units Volts needed to build any voltage reference

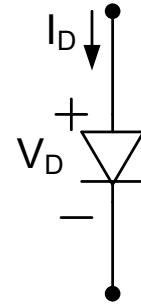
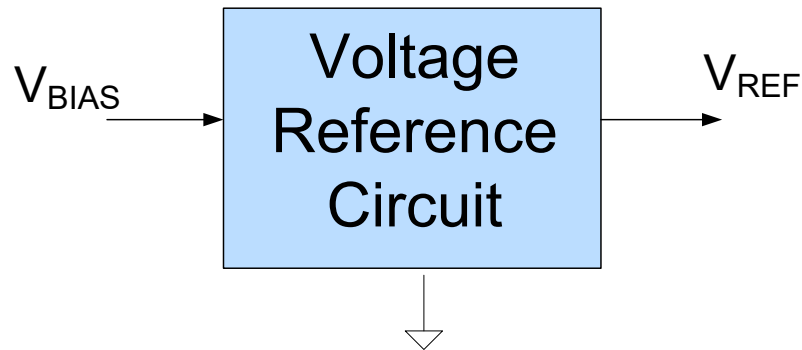
What variables available in a process have units volts?

$V_{DD}$ ,  $V_T$ ,  $V_D$  (diode),  $V_Z$ ,  $V_{BE}$ ,  $V_t$ ,  $V_{G0}$  ???

What variables which have units volts satisfy the desired properties of a voltage reference?  $V_{G0}$  and ??

How can a circuit be designed that “expresses” the desired variables?

# Voltage References



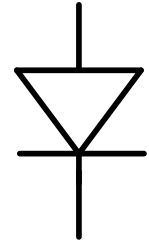
$V_{DD}$ ,  $V_T$ ,  $V_D$  (diode),  $V_Z$ ,  $V_{BE}$ ,  $V_t$ ,  $V_{G0}$  ???

How can a circuit be designed that “expresses” the desired variables?

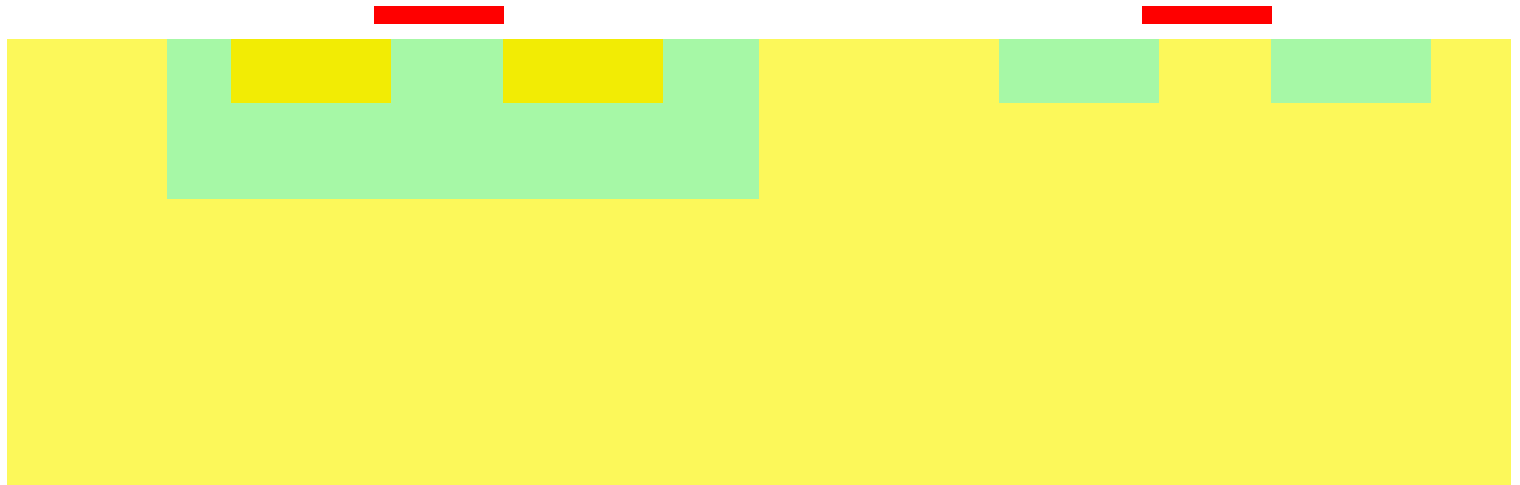
- $V_{G0}$  is deeply embedded in a device model with horrible temperature effects !
- Good diodes are not widely available in most MOS processes !

$$I_C = \tilde{J}_{SX} A T^m e^{\frac{-V_{G0}}{V_t}} e^{\frac{V_{BE}}{V_t}}$$

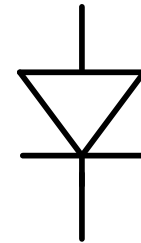
# Voltage References



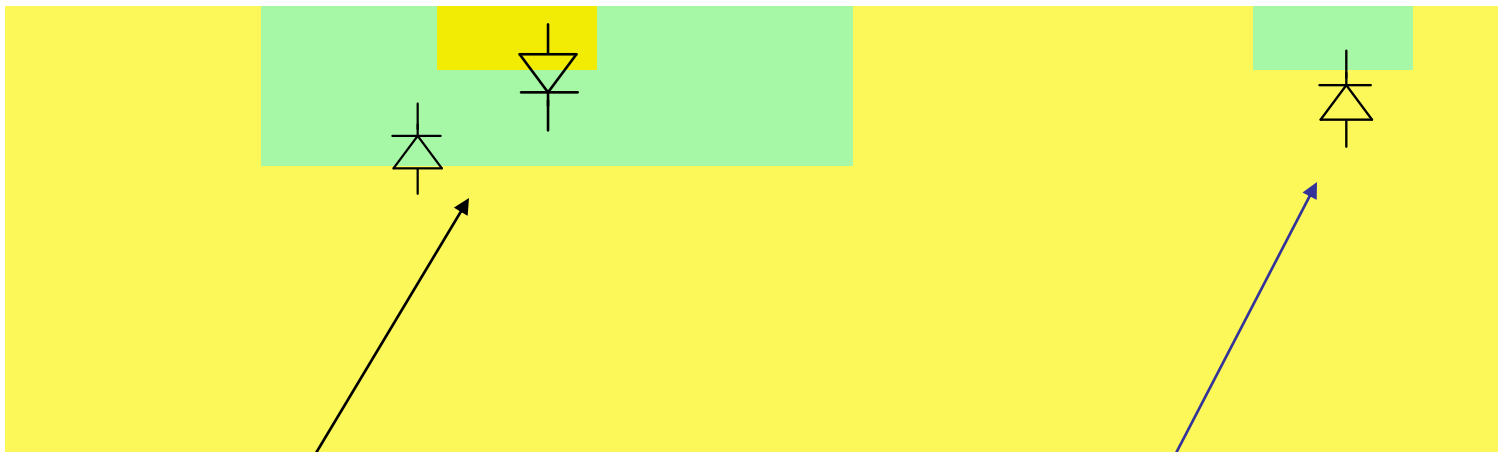
Good diodes are not widely available in most MOS processes !



# Voltage References



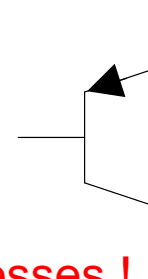
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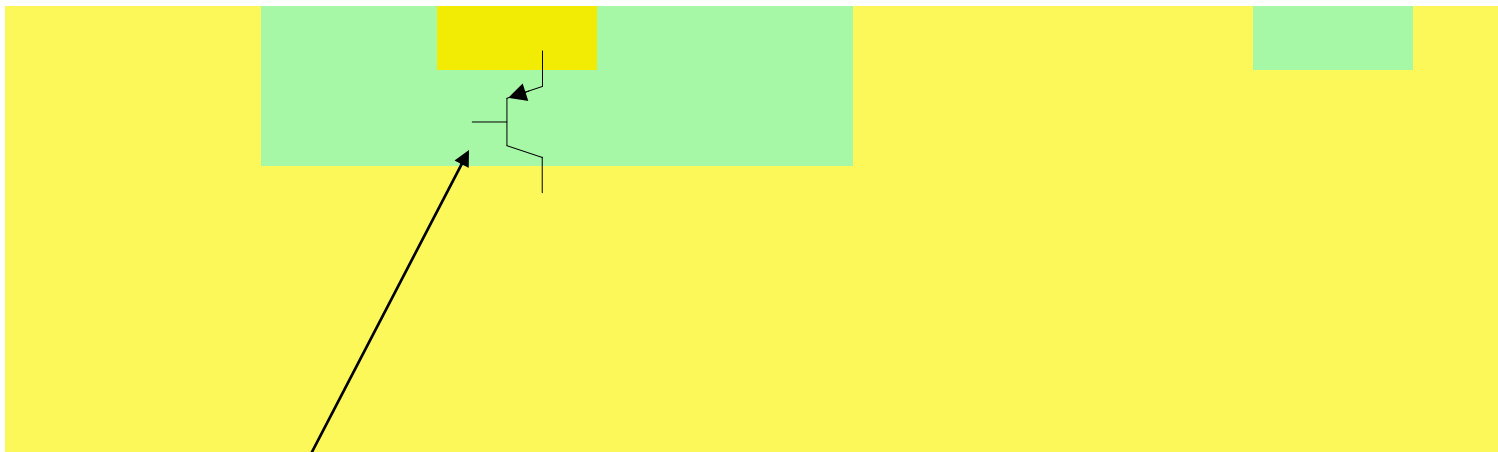
These diodes interact and actually form substrate pnp transistor

Not practical to forward bias junction

# Voltage References

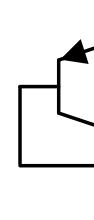


Good diodes are not widely available in most MOS processes !

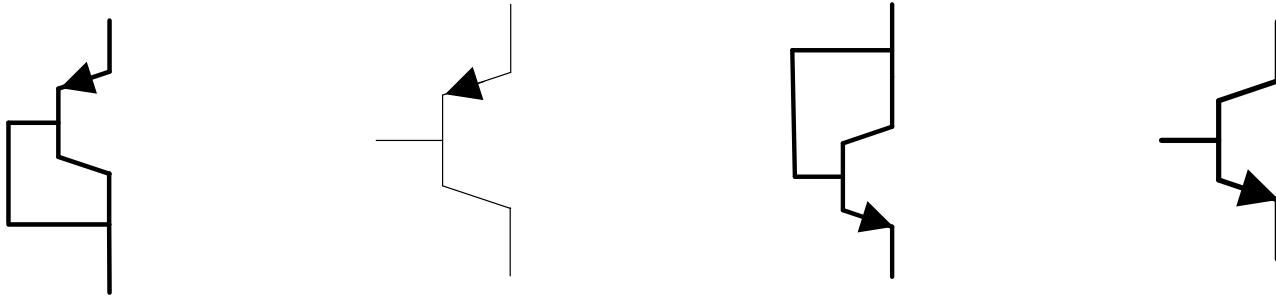


Substrate pnp transistor

Diode-connected  
substrate pnp



# Voltage References



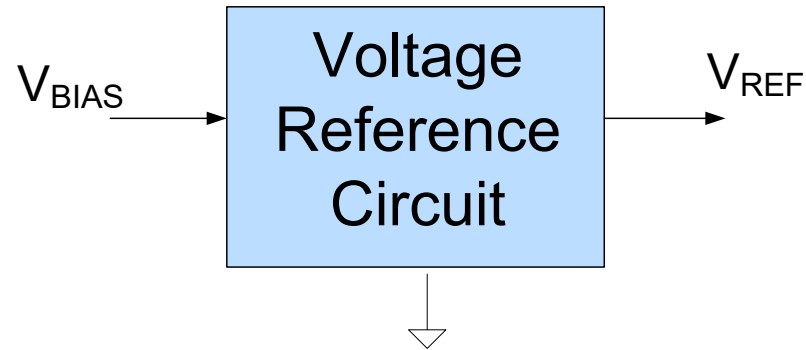
$$I_C = J_S A e^{\frac{V_{BE}}{V_t}}$$

$$J_S = \tilde{J}_{SX} \left[ T^m e^{\frac{-V_{G0}}{V_t}} \right]$$

Bandgap Voltage Appears in BJT Model Equation as well

$$I_C(T) = \left( \tilde{J}_{SX} A \left[ T^m e^{\frac{-V_{G0}}{V_t}} \right] \right) e^{\frac{V_{BE}(T)}{V_t}}$$

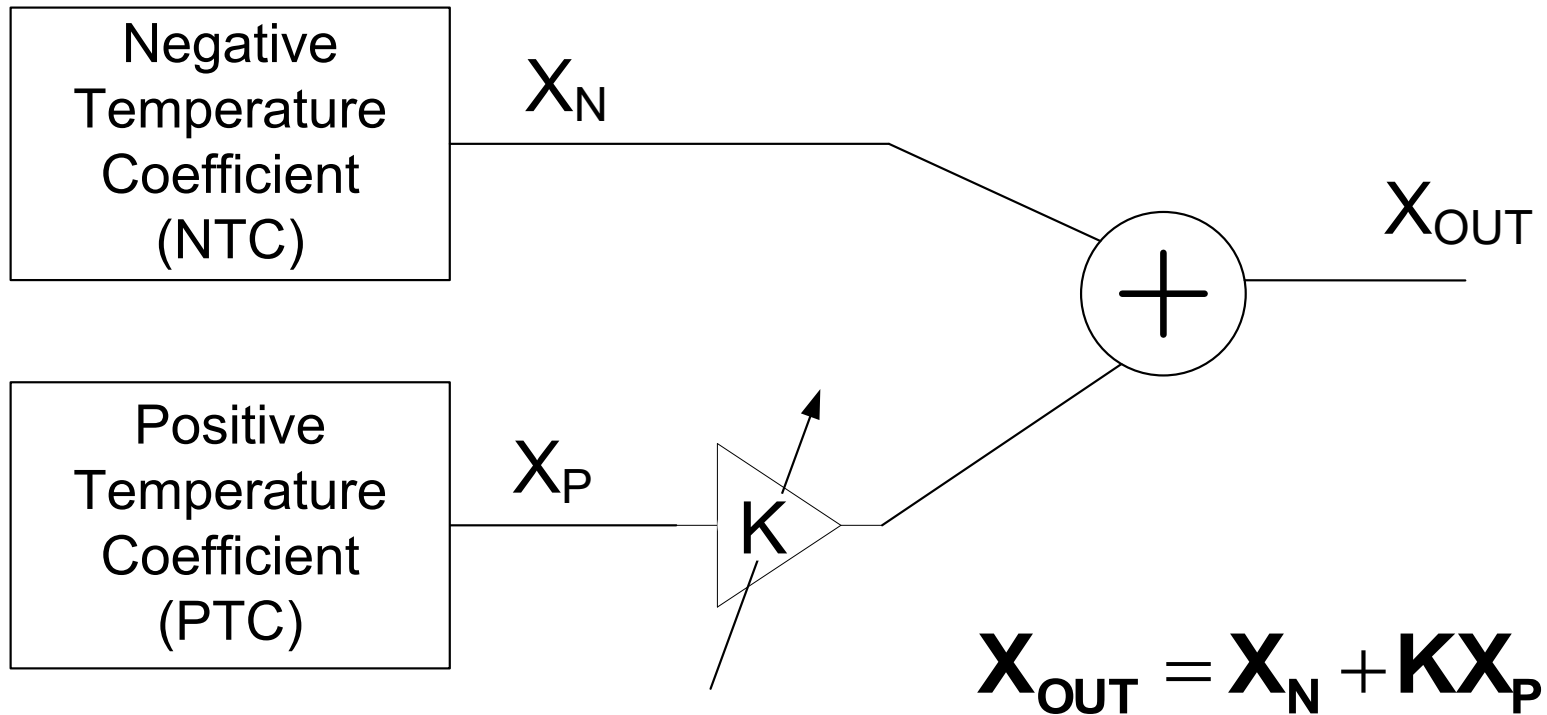
# Voltage References



Voltage references that “express” the bandgap voltage are termed “Bandgap References”

- $V_{G0}$  is deeply embedded in a device model with horrible temperature effects !
- Good BJTs are not widely available in most MOS processes but the substrate pnp is available !

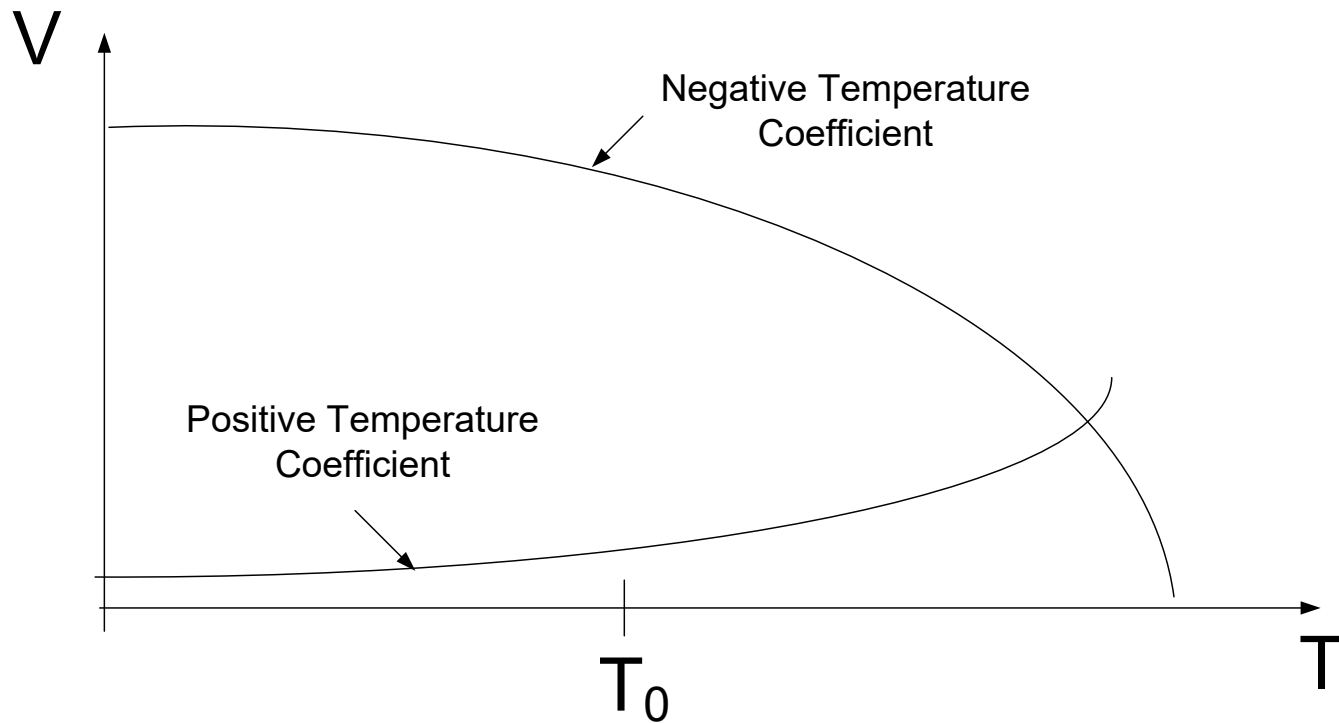
# Standard Approach to Building Voltage References



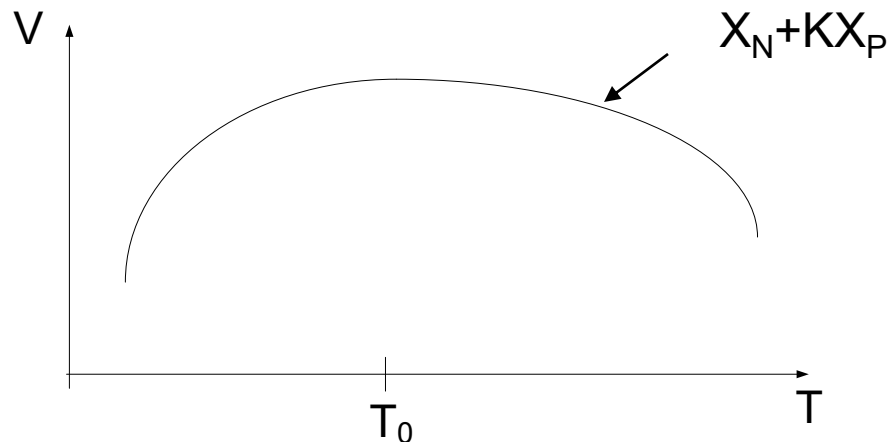
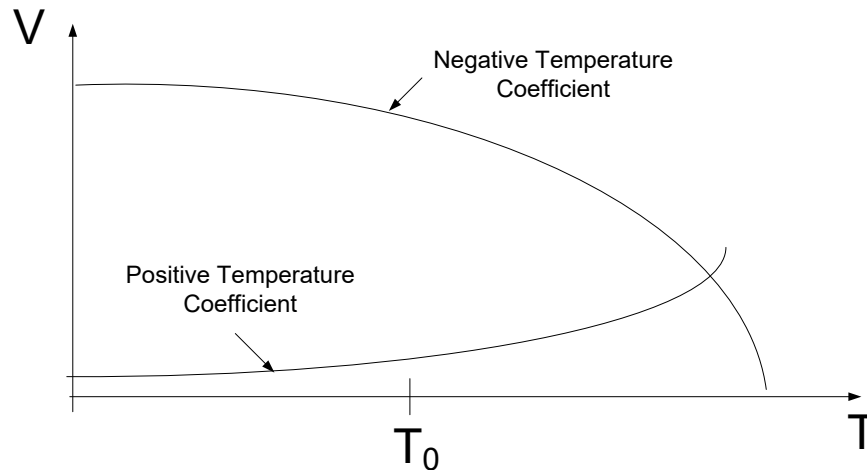
Pick  $K$  so that at some temperature  $T_0$ ,  $\left. \frac{\partial(X_N + KX_P)}{\partial T} \right|_{T=T_0} = 0$



# Standard Approach to Building Voltage References



# Standard Approach to Building Voltage References



Select  $K$  so that

$$\left. \frac{\partial (X_N + KX_P)}{\partial T} \right|_{T=T_0} = 0$$

# Bandgap Voltage References

Consider two BJTs (or diodes)



$$I_C(T) = \left( \tilde{I}_{SX} \left[ T^m e^{\frac{-V_{G0}}{V_t}} \right] \right) e^{\frac{V_{BE}(T)}{V_t}} \quad \dots \dots \dots \text{Exponential form}$$

$$V_{BE} = V_{G0} + V_t \ln \left( \frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T \quad \dots \dots \dots \text{Logarithmic form}$$

$$V_{BE2} - V_{BE1} = \Delta V_{BE} = \left[ \frac{k}{q} \ln \left( \frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right) \right] T$$

If the  $\frac{I_{C2} A_{E1}}{I_{C1} A_{E2}}$  ratio is constant and  $>1$ , the TC of  $\Delta V_{BE}$  is positive

$\Delta V_{BE}$  is termed a PTAT voltage (Proportional to Absolute Temperature)

This relationship applies irrespective of how temperature dependent  $I_{C1}$  and  $I_{C2}$  may be provided the ratio is constant !!

# Bandgap Voltage References

Consider two BJTs (or diodes)



$$V_{BE2} - V_{BE1} = \Delta V_{BE} = \left[ \frac{k}{q} \ln \left( \frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right) \right] T$$

$$\frac{\partial (V_{BE2} - V_{BE1})}{\partial T} = \frac{k}{q} \ln \left( \frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right)$$

At room temperature if  $\ln \left( \frac{I_{C2} A_{E1}}{I_{C1} A_{E2}} \right) = 1$

$$V_{BE2} - V_{BE1} = [8.6 \times 10^{-5} \times 300] = 25.8 \text{ mV}$$

and

$$\left. \frac{\partial (V_{BE2} - V_{BE1})}{\partial T} \right|_{T=T_0=300^\circ\text{K}} = 8.6 \times 10^{-5} = 86 \mu\text{V}/^\circ\text{C}$$

The temperature coefficient of the PTAT voltage is rather small

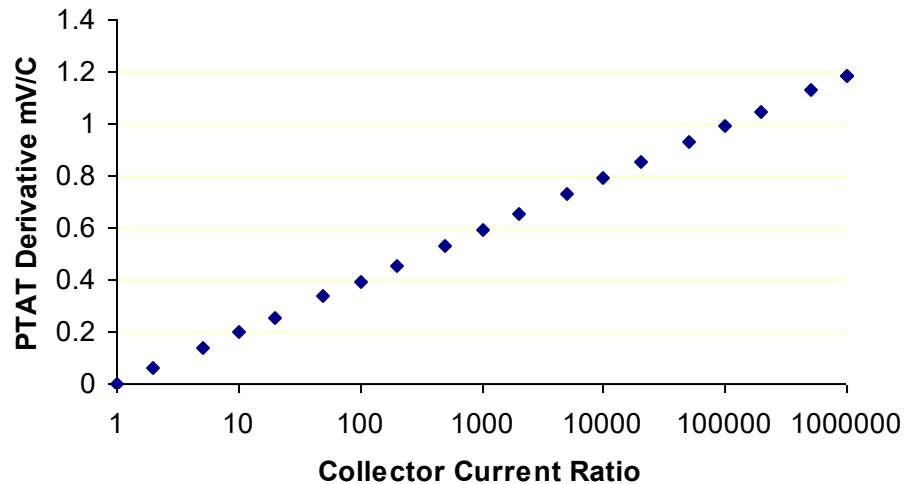
# Bandgap Voltage References

Consider two BJTs (or diodes)



$$\frac{\partial(V_{BE2} - V_{BE1})}{\partial T} = \frac{k}{q} \ln\left(\frac{I_{C2}}{I_{C1}}\right)$$

At room temperature if  $A_{E1} = A_{E2}$



The temperature coefficient of the PTAT voltage is rather small even if large collector current ratios are used

# Bandgap Voltage References

Consider two BJTs (or diodes)      Typically,  $m=2.3$ ,  $V_{G0}=1.2V$       Assume  $V_{BE} \approx 0.65V$



$$I_C(T) = \left( \tilde{J}_{SX} A_E \left[ T^m e^{\frac{-V_{G0}}{V_t}} \right] \right) e^{\frac{V_{BE}(T)}{V_t}}$$

$$V_{BE} = V_{G0} + V_t \ln \left( \frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

If  $I_C$  is independent of temperature, it follows that

$$\frac{\partial V_{BE}}{\partial T} = \frac{k}{q} \left[ -m + \left( \frac{V_{BE} - V_{G0}}{V_t} \right) \right]$$

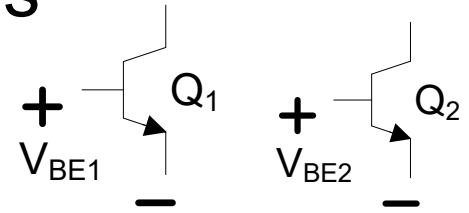
$$\left. \frac{\partial V_{BE}}{\partial T} \right|_{T=T_0=300^\circ K} \cong 8.6 \times 10^{-5} \left[ -2.3 + \left( \frac{0.65 - 1.2}{25 \text{mV}} \right) \right] \cong -2.1 \text{mV}/^\circ \text{C}$$

# Bandgap Voltage References

Consider two BJTs (or diodes)

Typically,  $m=2.3$ ,  $V_{G0}=1.2V$

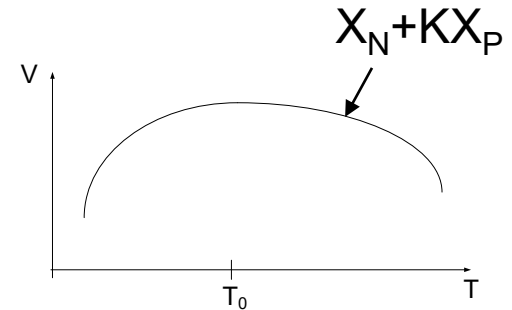
Assume  $V_{BE} \approx 0.65V$



Thus if  $I_C$  independent of temperature and if  $\ln\left(\frac{I_{C2}A_{E1}}{I_{C1}A_{E2}}\right) = 1$

$$\left. \frac{\partial V_{BE}}{\partial T} \right|_{T=T_0=300^\circ K} \cong -2.1 \text{ mV}/^\circ\text{C}$$

$$\left. \frac{\partial (V_{BE2} - V_{BE1})}{\partial T} \right|_{T=T_0=300^\circ K} = 86 \mu\text{V}/^\circ\text{C}$$



Magnitude of TC of PTAT source is much smaller than that of  $V_{BE}$  source

Define:

$$X_N = V_{BE} \quad X_P = V_{BE2} - V_{BE1}$$

Create circuit with:

$$X_{OUT} = X_N + KX_P$$

If we want  $\left. \frac{\partial (X_N + KX_P)}{\partial T} \right|_{T=T_0} = 0$

K will need to be large

# Bandgap Voltage References

Consider two BJTs (or diodes)



$$V_{BE} = V_{G0} + V_t \ln \left( \frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

It was just shown that if  $I_C$  is independent of temperature

$$\left. \frac{\partial V_{BE}}{\partial T} \right|_{T=T_0=300^\circ\text{K}} \cong 8.6 \times 10^{-5} \left[ -2.3 + \left( \frac{0.65 - 1.2}{25\text{mV}} \right) \right] \cong -2.1\text{mV}/^\circ\text{C}$$

If  $I_C$  is reasonably independent of temperature,  $V_{BE}$  will still provide a negative TC

Even if  $I_C$  is highly dependent on temperature,  $V_{BE}$  will still provide a negative TC

Observe  $V_{G0}$  appears prominently in  $V_{BE}$



# Bandgap Voltage References

Consider two BJTs (or diodes)

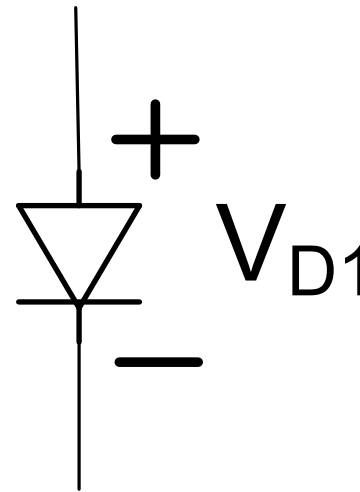
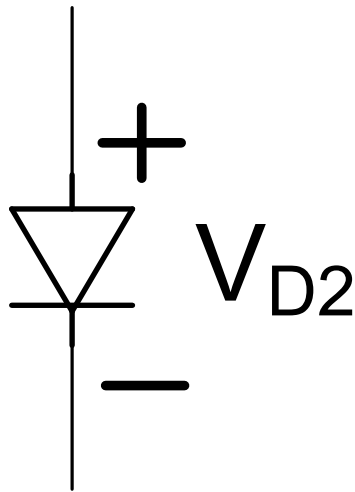


## Key observation about diodes and diode-connected BJTs

1. If ratio of currents in two devices is constant,  $\Delta V_{BE}$  can be PTAT independent of the temperature dependence of the currents and sensitivity of  $\Delta V_{BE}$  to T is small
2.  $V_{BE}$  has a negative temperature coefficient for a wide range of temperature dependent or temperature independent currents and sensitivity is much larger than that of  $\Delta V_{BE}$

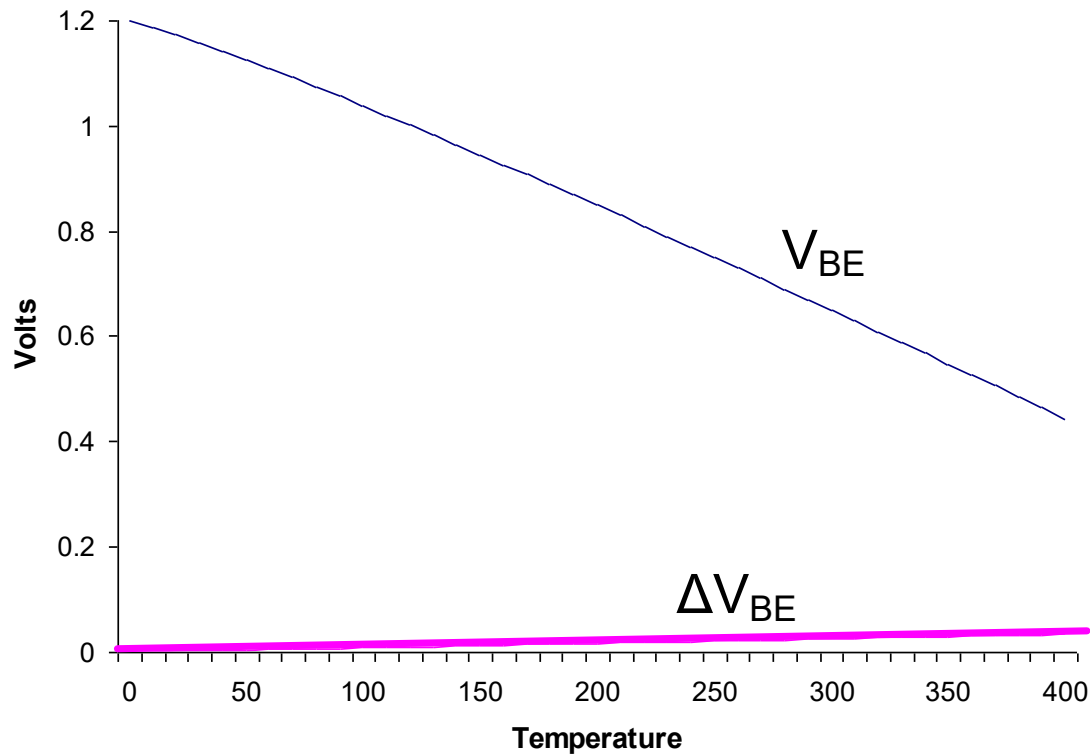
# Bandgap Reference Circuits

- Circuits that implement  $\Delta V_{BE}$  and  $V_{BE}$  or  $\Delta V_D$  and  $V_D$  widely used to build bandgap references

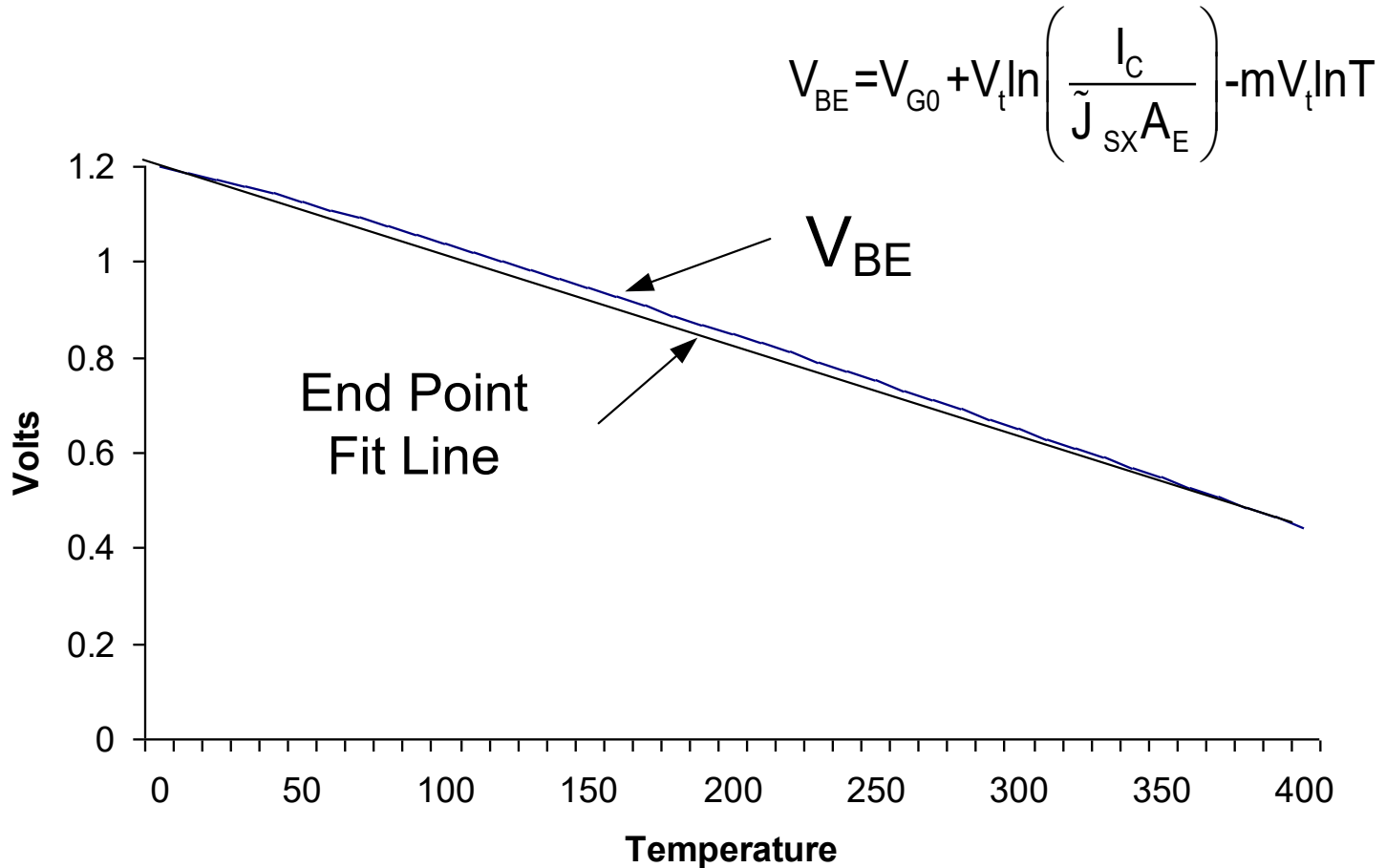


# $V_{BE}$ and $\Delta V_{BE}$ with constant $I_C$

$$V_{BE} = V_{G0} + V_t \ln \left( \frac{I_C}{\tilde{J}_{SX} A_E} \right) - m V_t \ln T$$

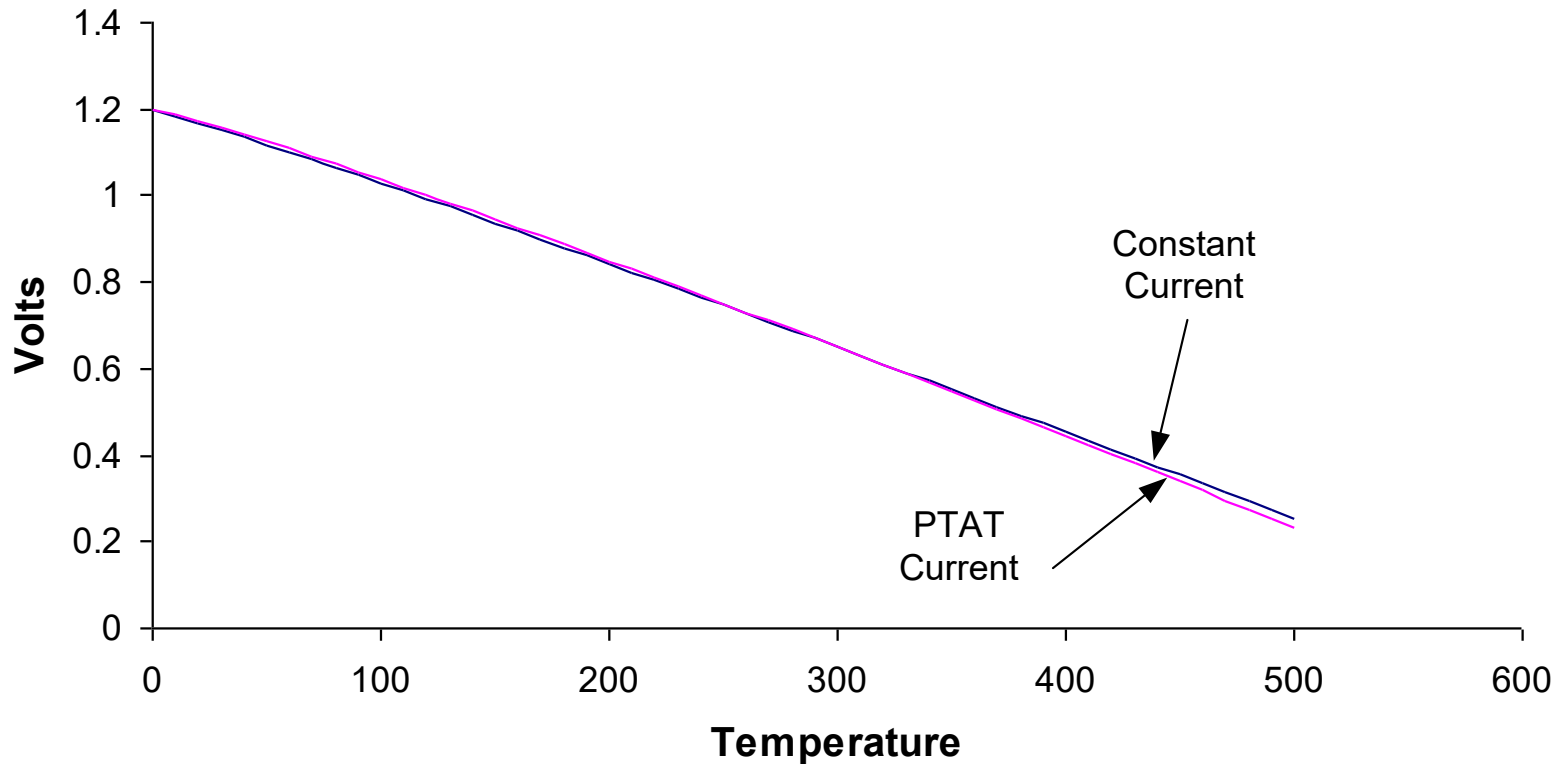


# $V_{BE}$ plot for constant $I_C$



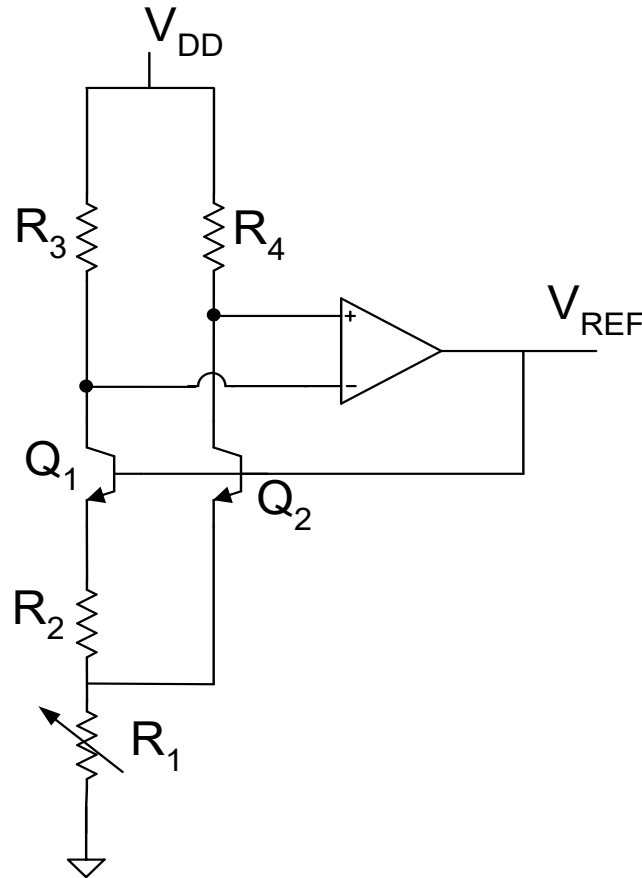
Combined effects of the  $T$  and  $T \ln T$  terms in  $V_{BE}$  is nearly linear dependent on  $T$

# Comparison of $V_{BE}$ with constant current and PTAT current



Even if  $I_C$  is highly-dependent on current, temperature dependence of  $V_{BE}$  is still nearly linearly dependent upon  $T$

# Early Bandgap Reference (and still widely used!)

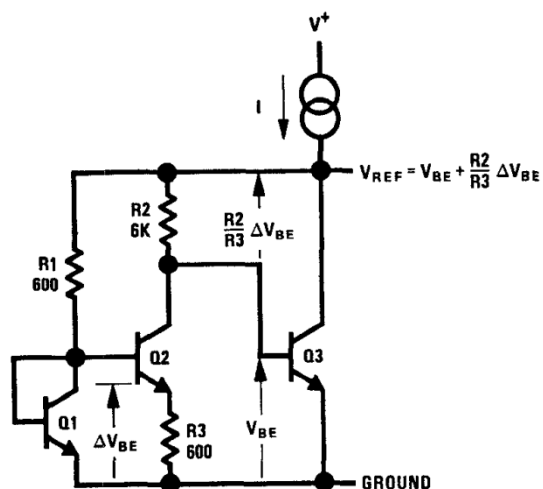


P. Brokaw, "A Simple Three-Terminal IC Bandgap Reference", IEEE Journal of Solid State Circuits, Vol. 9, pp. 388-393, Dec. 1974.

- Brokaw coined term "bandgap reference" when referring to this circuit
- Properties very similar circuits introduced by Widlar and Kujik a small while earlier
- Paper submitted May 1974, Widlar paper submitted March 1970

# New Developments in IC Voltage Regulators

ROBERT J. WIDLAR



Widlar retired in Dec. 1970 at the age of 33

Widlar observed  $\Delta V_{BE}$  is PTAT in 1965

1 R. J. Widlar, "Some circuit design techniques for linear integrated circuits," *IEEE Trans. Circuit Theory*, vol. CT-12, pp. 586-590, December 1965.

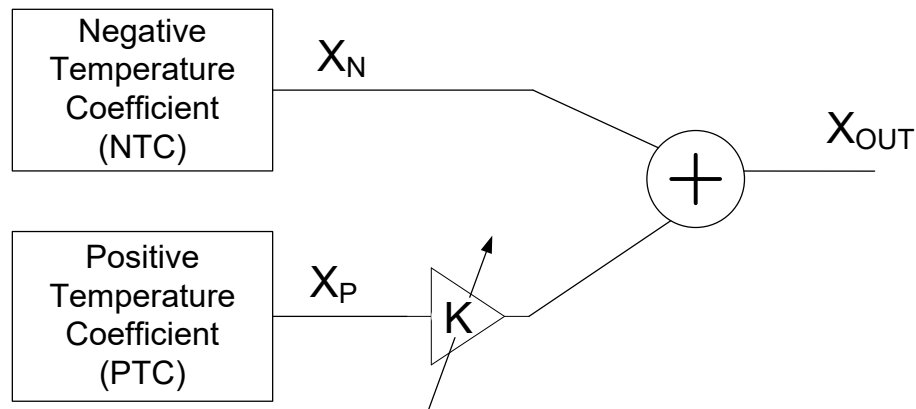
# Most Published Analysis of Bandgap Circuits

$V_{REF}$  often expressed as:

$$V_{REF} = V_{G0} + \frac{T}{T_0} (V_{BE0} - V_{G0}) + K \frac{kT}{q} \ln\left(\frac{J_2}{J_1}\right) + (m-1) \frac{kT}{q} \ln\left(\frac{T_0}{T}\right)$$

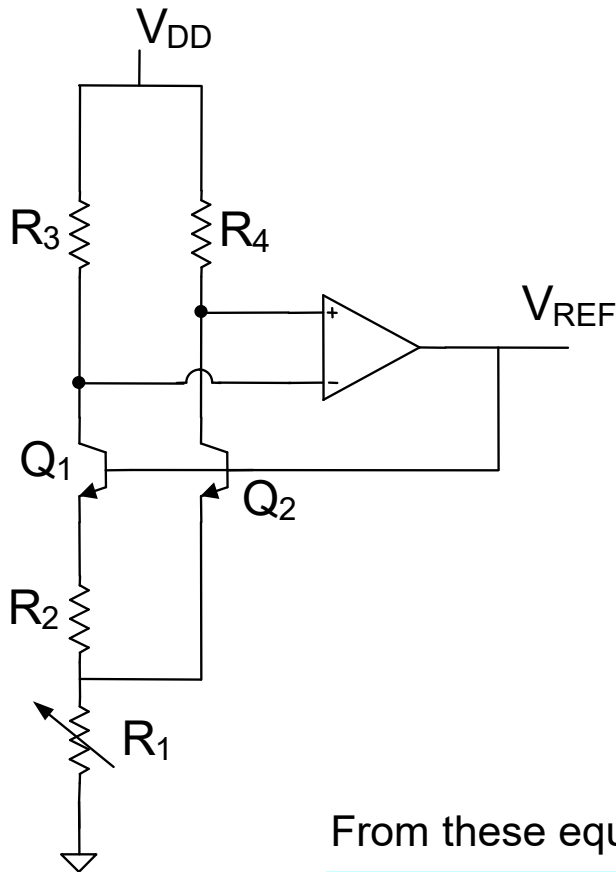
where K is the gain of the PTAT signal

(Not a solution and dependent upon both  $T_0$  and  $V_{BE0}$ )





# First Bandgap Reference (and still widely used!)



$$I_{E1} R_2 + V_{BE1} = V_{BE2}$$

$$V_{REF} = V_{BE2} + (I_{E1} + I_{E2}) R_1$$

$$I_{C1} = \frac{V_{DD} - V_{C2}}{R_3}$$

$$I_{C2} = \frac{V_{DD} - V_{C2}}{R_4}$$

$$I_{C1} = \alpha_1 I_{E1}$$

$$I_{C2} = \alpha_2 I_{E2}$$

$$I_{E1} = I_{E2} \left[ \frac{\alpha_2 R_4}{\alpha_1 R_3} \right]$$

$$\alpha = \frac{\beta}{1 + \beta}$$

$$I_{C1} = I_{C2} \left[ \frac{R_4}{R_3} \right]$$

From these equations can show

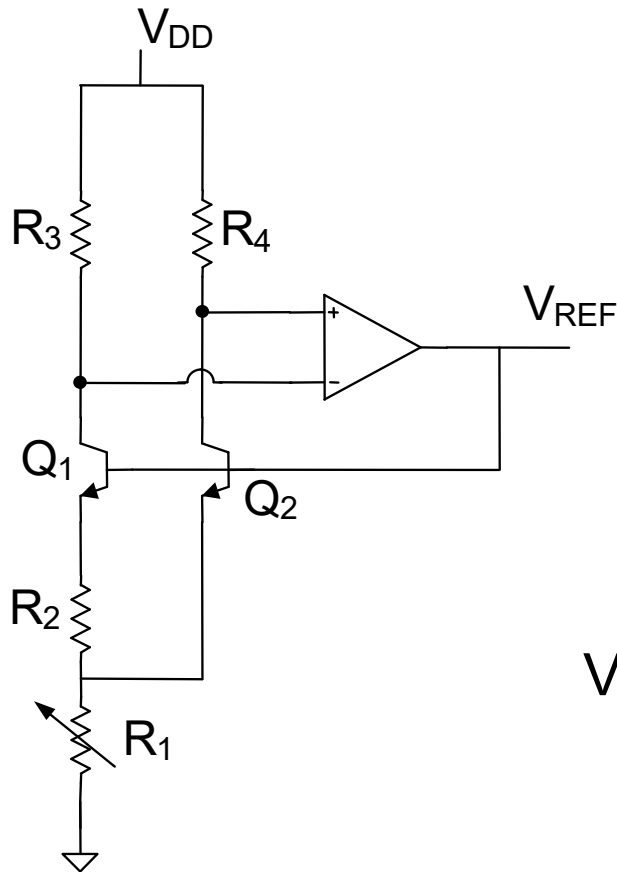
$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

Not a solution but can provide zero temp slope by adjusting  $R_1$

# First Bandgap Reference (and still widely used!)

Will now obtain solution for  $V_{REF}$  (in terms of component values and model parameters)

$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$



$$V_{BE1} = V_{G0} + V_t \ln \left( \frac{I_{C1}}{\tilde{J}_{SX} A_{E1}} \right) - m V_t \ln T$$

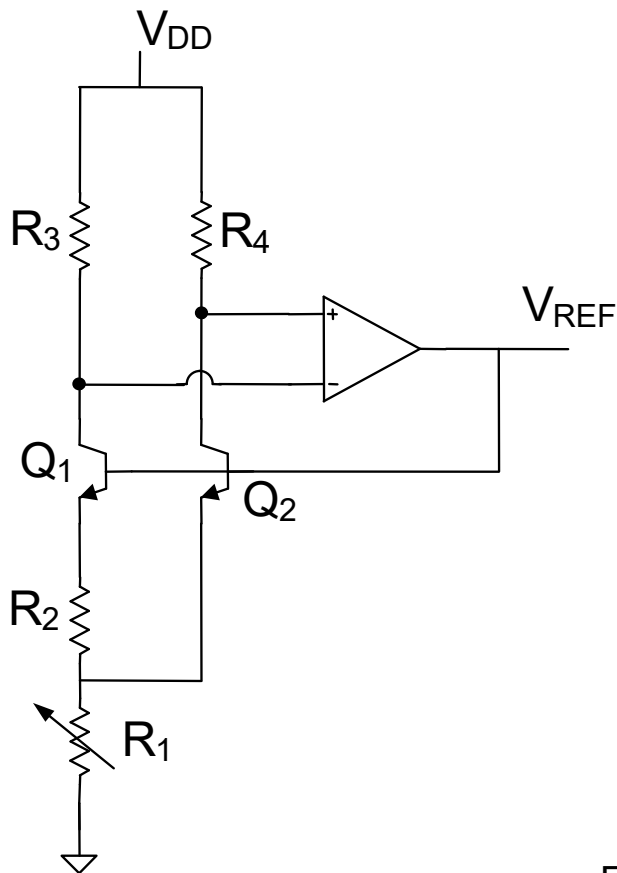
$$V_{BE2} = V_{G0} + V_t \ln \left( \frac{I_{C2}}{\tilde{J}_{SX} A_{E2}} \right) - m V_t \ln T$$

$$I_{C1} = I_{C2} \left[ \frac{R_4}{R_3} \right]$$

$$V_{BE2} - V_{BE1} = \Delta V_{BE} = \left[ \frac{k}{q} \ln \left( \frac{A_{E1}}{A_{E2}} \left[ \frac{R_3}{R_4} \right] \right) \right] T$$

# First Bandgap Reference (and still widely used!)

Will now obtain solution for  $V_{REF}$  (in terms of component values and model parameters)



$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

$$V_{BE1} = V_{G0} + V_t \ln \left( \frac{I_{C1}}{\tilde{J}_{SX} A_{E1}} \right) - m V_t \ln T$$

$$V_{BE2} = V_{G0} + V_t \ln \left( \frac{I_{C2}}{\tilde{J}_{SX} A_{E2}} \right) - m V_t \ln T$$

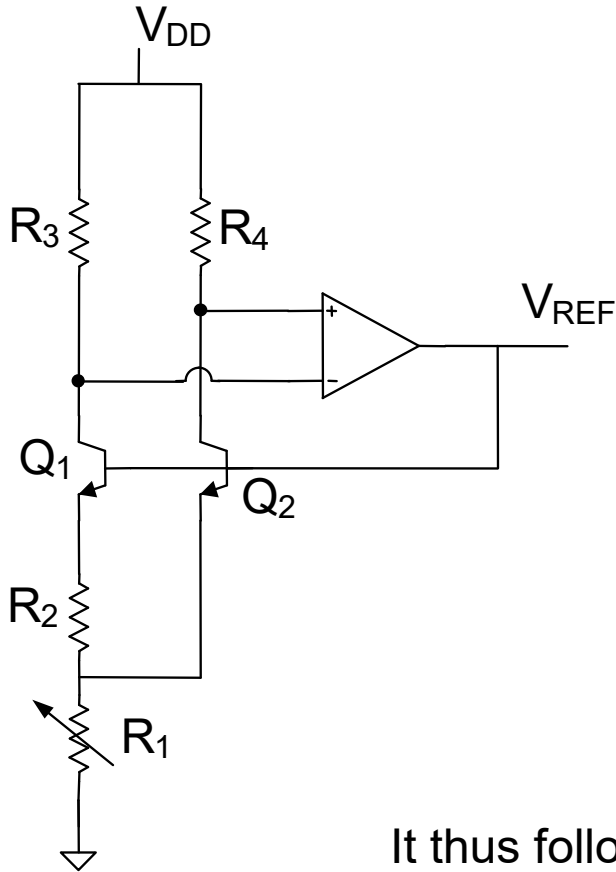
$$I_{C1} = I_{C2} \left[ \frac{R_4}{R_3} \right]$$

$$\frac{I_{C1}}{\alpha_1} R_2 + V_{BE1} = V_{BE2}$$

From the expression for  $V_{BE2}$  and some routine but tedious manipulations it follows that

$$V_{BE2} = V_{G0} + (1-m) V_t \ln T + V_t \ln \left( \frac{k}{q} \frac{\alpha_1}{R_2 A_{E2} \tilde{J}_{SX}} \frac{R_3}{R_4} \ln \left( \frac{A_{E1} R_3}{A_{E2} R_4} \right) \right)$$

# First Bandgap Reference (and still widely used!)



$$V_{\text{REF}} = V_{\text{BE2}} + (V_{\text{BE2}} - V_{\text{BE1}}) \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

$$V_{\text{BE2}} - V_{\text{BE1}} = \left[ \frac{k}{q} \ln \left( \frac{A_{\text{E1}}}{A_{\text{E2}}} \left[ \frac{R_3}{R_4} \right] \right) \right] T$$

$$V_{\text{BE2}} = V_{\text{G0}} + (1-m)V_t \ln T + V_t \ln \left( \frac{k}{q} \frac{\alpha_1}{R_2 A_{\text{E2}} \tilde{J}_{\text{SX}}} \frac{R_3}{R_4} \ln \left( \frac{A_{\text{E1}} R_3}{A_{\text{E2}} R_4} \right) \right)$$

It thus follows that:

$$V_{\text{REF}} = V_{\text{G0}} + V_t \ln \left\{ \frac{\alpha_1 R_3}{R_2 R_4} T \frac{k}{q} \ln \left( \frac{A_{\text{E1}} R_3}{A_{\text{E2}} R_4} \right) \right\} - V_t \left( \ln(\tilde{J}_{\text{SX2}}) + m \ln T \right) + \left[ \frac{k}{q} \ln \left( \frac{A_{\text{E1}}}{A_{\text{E2}}} \left( \frac{R_3}{R_4} \right) \right) \right] \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right] T$$

# First Bandgap Reference (and still widely used!)

$$V_{REF} = V_{BE2} + (V_{BE2} - V_{BE1}) \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right]$$

$$V_{REF} = V_{G0} + V_t \ln \left\{ \frac{\alpha_1 R_3}{R_2 R_4} T \frac{k}{q} \ln \left( \frac{A_{E1} R_3}{A_{E2} R_4} \right) \right\} - V_t (\ln(\tilde{I}_{SK2}) + m \ln T) + \left[ \frac{k}{q} \ln \left( \frac{A_{E1}}{A_{E2}} \left( \frac{R_3}{R_4} \right) \right) \right] \left[ \frac{R_1}{R_2} \left( 1 + \frac{\alpha_1 R_3}{\alpha_2 R_4} \right) \right] T$$

This can be expressed after some tedious algebraic manipulations as

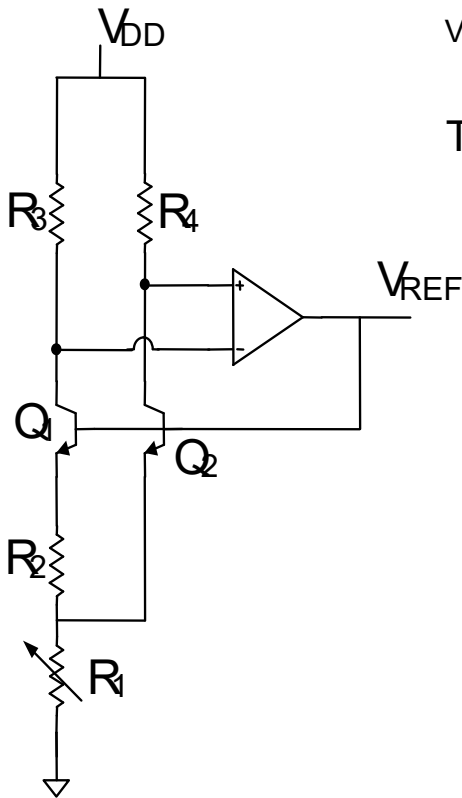
$$V_{REF} = a_1 + b_1 T + c_1 T \ln T$$

where

$$a_1 = V_{G0}$$

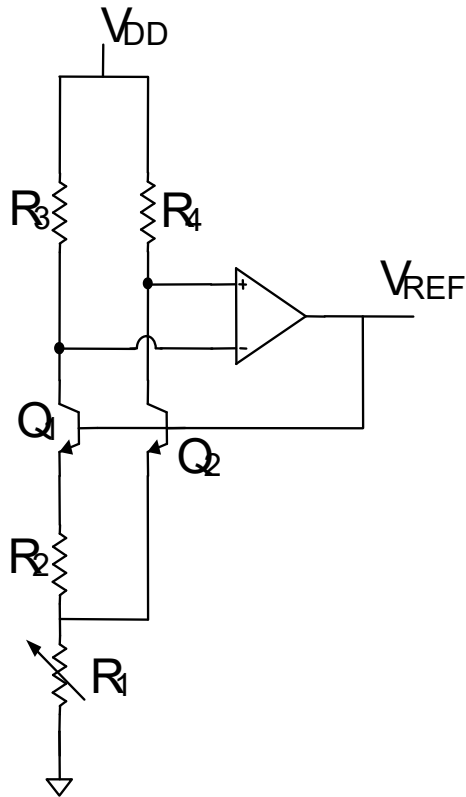
$$b_1 = \frac{k}{q} \left( \frac{R_1}{R_2} \left( 1 + \frac{R_3 \alpha_1}{R_4 \alpha_2} \right) \ln \left( \frac{R_3 A_{E1}}{R_4 A_{E2}} \right) + \ln \left( \frac{k R_3}{q R_4} \alpha_1 \frac{\ln \left( \frac{R_3 A_{E1}}{R_1 A_{E2}} \right)}{\tilde{I}_{SK2} R_2} \right) \right)$$

$$c_1 = \frac{k}{q} (1 - m)$$



# First Bandgap Reference (and still widely used!)

$$V_{REF} = a_1 + b_1 T + c_1 T \ln T$$



$$a_1 = V_{GO}$$

$$b_1 = \frac{k}{q} \left[ \frac{R_1}{R_2} \left( 1 + \frac{R_3 \alpha_1}{R_4 \alpha_2} \right) \ln \left( \frac{R_3 A_{E1}}{R_4 A_{E2}} \right) + \ln \left( \frac{k R_3 \alpha_1}{q R_4} \frac{\ln \left( \frac{R_3 A_{E1}}{R_1 A_{E2}} \right)}{\tilde{I}_{SK2} R_2} \right) \right]$$

$$c_1 = \frac{k}{q} (1 - m)$$

$$\frac{dV_{REF}}{dT} = b_1 + c_1 (1 + \ln T) = 0$$

$$T_{INF} = e^{-\left(1 + \frac{b_1}{c_1}\right)}$$

$$b_1 = -c_1 (1 + \ln T_{INF})$$

at  $T_{INF}$   $V_{REF} = a_1 - c_1 T_{INF}$

$$V_{REF} = V_{GO} + \frac{k T_{INF}}{q} (m - 1)$$

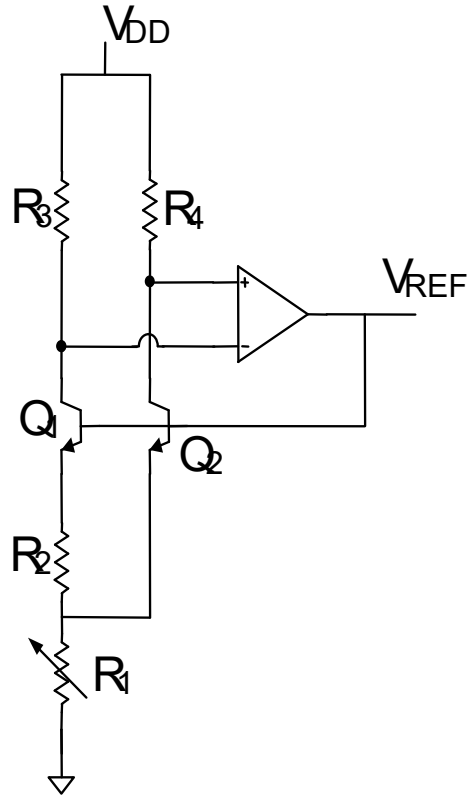
$$\frac{k T_{INF}}{q} (m - 1)$$

is small



Nearly  $V_{GO}$  output at  $T_{INF}$

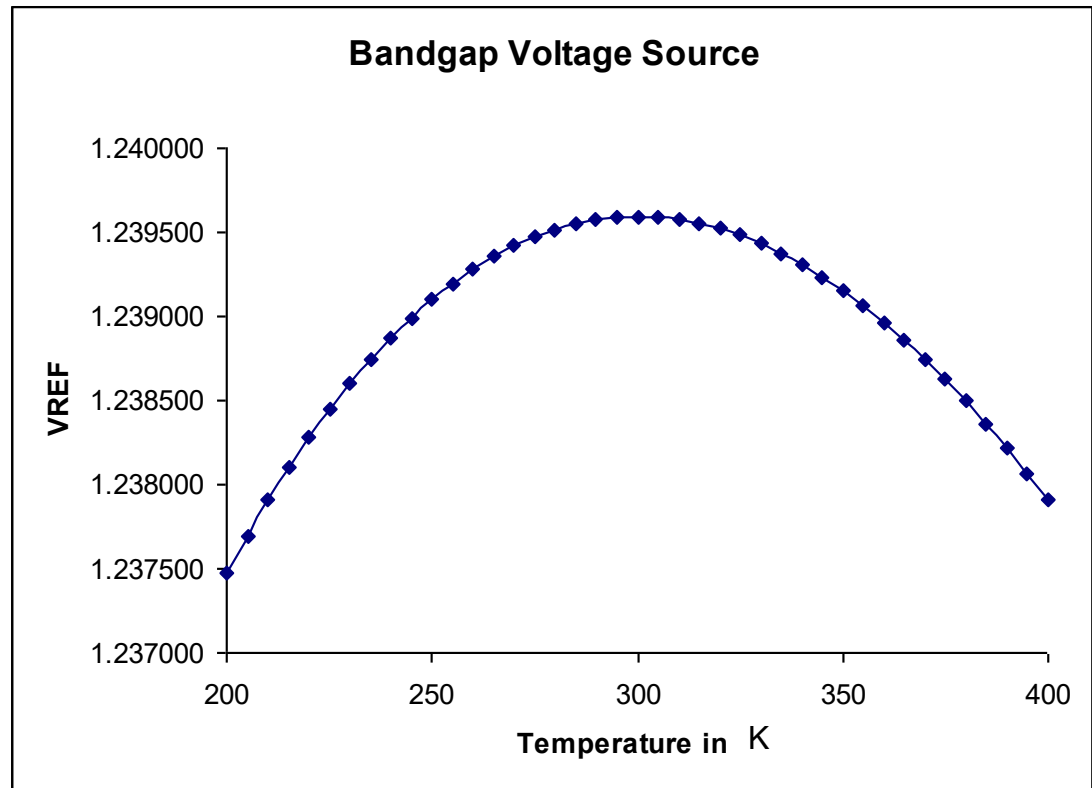
# First Bandgap Reference (and still widely used!)



VGO	1.206
TO	300
VBEO2	0.65
m-1	1.3
k/q	8.61E-05

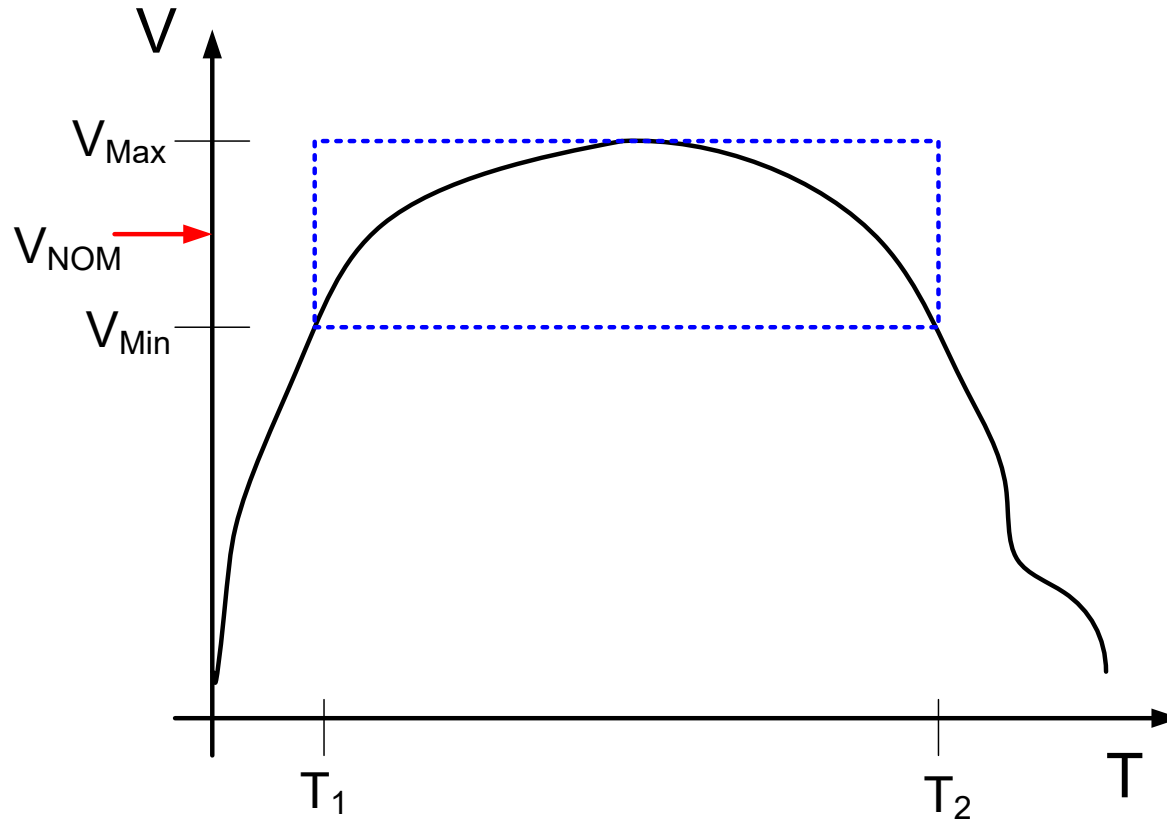
$$V_{REF} = a_1 + b_1T + c_1T \ln T$$

$$V_{REF}(T_{INF}) = V_{G0} + \frac{kT_{INF}}{q}(m-1)$$



Only 2mV change over 200°C temp range !

# Temperature Coefficient

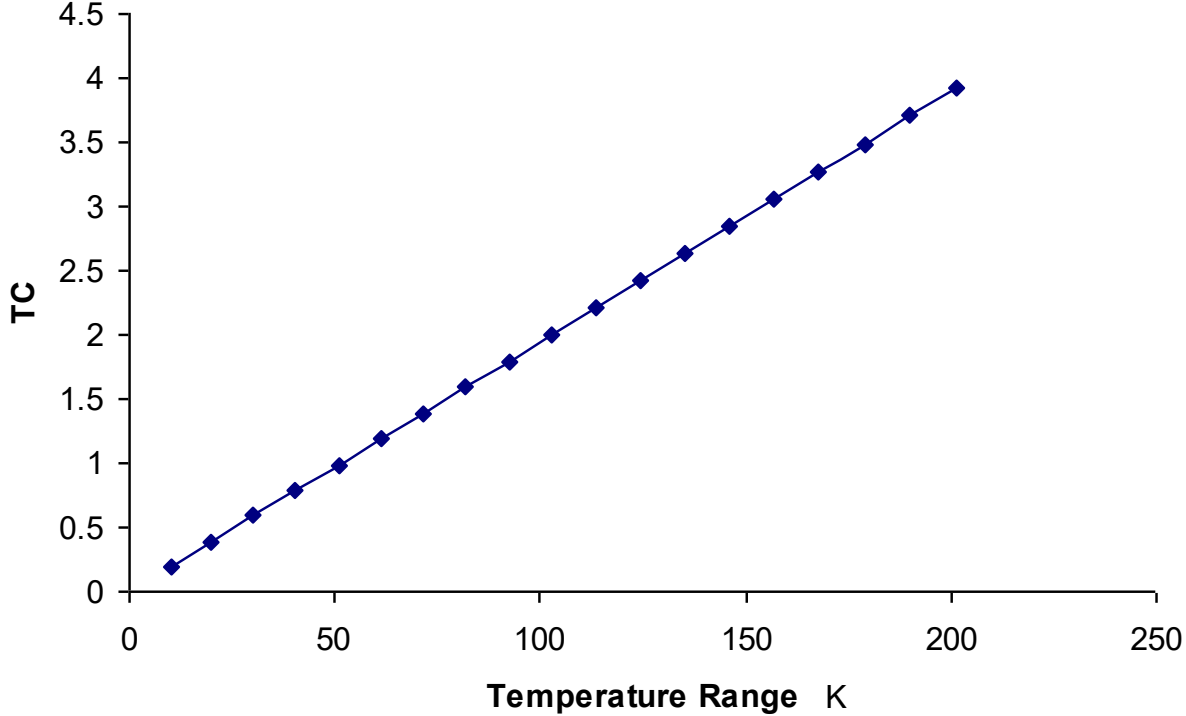


$$TC = \frac{V_{MAX} - V_{MIN}}{T_2 - T_1}$$

$$TC_{ppm} = \frac{V_{MAX} - V_{MIN}}{V_{NOM}(T_2 - T_1)} 10^6$$



**TC of Bandgap Reference (+/- ppm/C)**





# Bamba Bandgap Reference

$$I_{R0} = \frac{\Delta V_{BE}}{R_0}$$

$$I_{R1} = \frac{V_{BE1}}{R_1}$$

$$I_{R2} = I_{R1}$$

$$I_2 = I_{R0} + I_{R2}$$

$$I_3 = KI_2 \quad \text{K is the ratio of } I_3 \text{ to } I_2$$

$$V_{REF} = \theta I_3 R_4$$

Substituting, we obtain

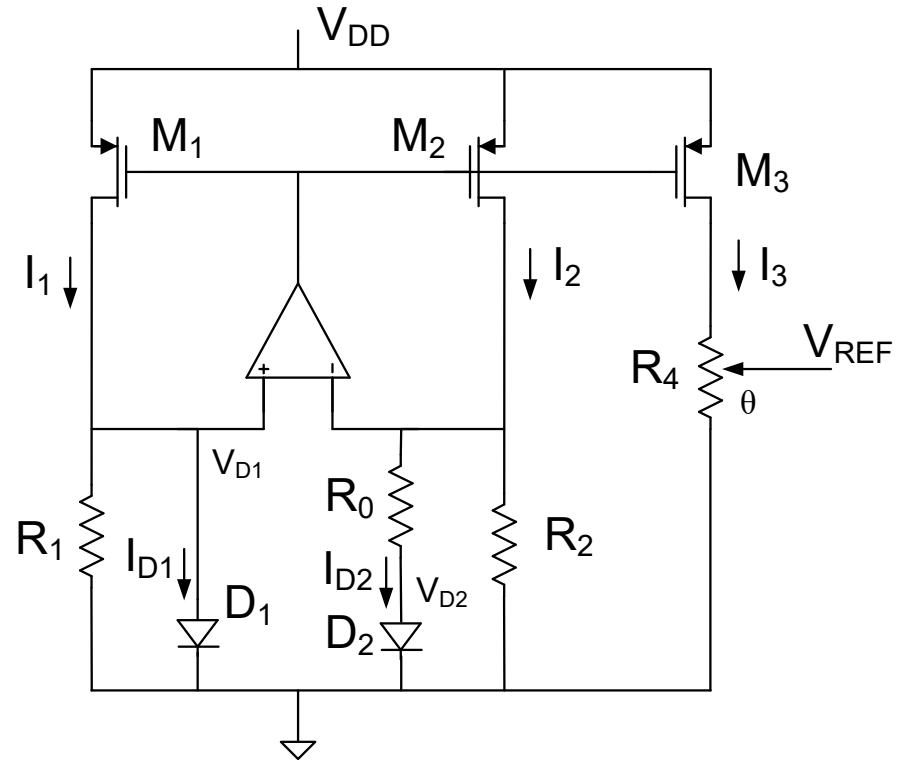
$$V_{REF} = \theta K R_4 \left( \frac{V_{BE}}{R_1} + \frac{\Delta V_{BE}}{R_0} \right)$$



$$V_{REF} = \theta K \frac{R_4}{R_1} \left( V_{BE} + \frac{R_1}{R_0} \Delta V_{BE} \right)$$

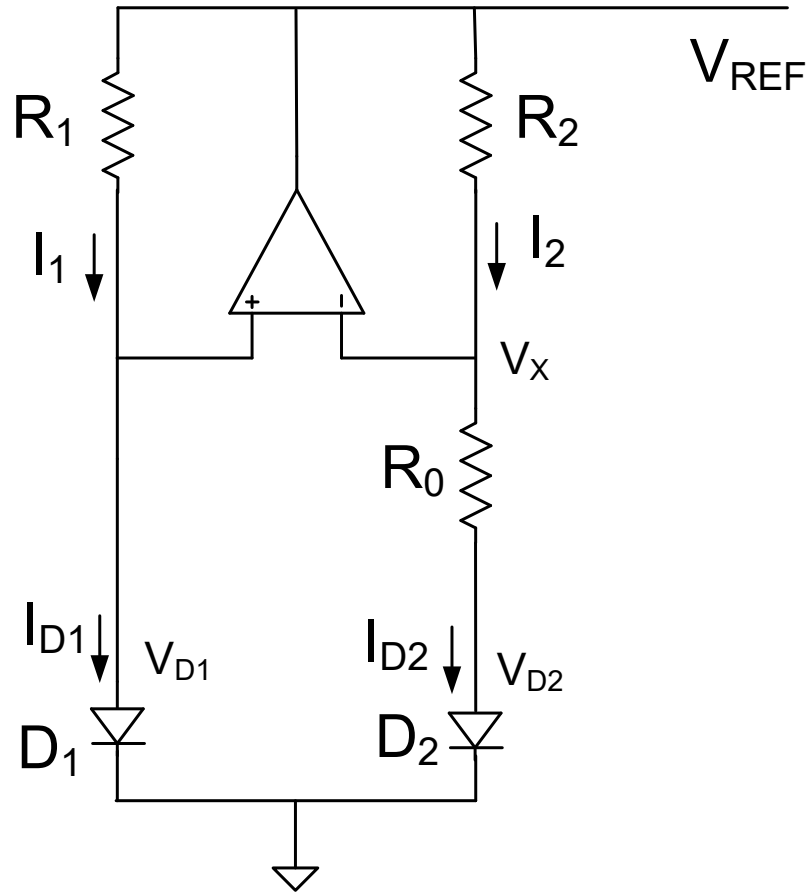
With some tedious algebra, it follows that  $V_{REF} = a_{11} + b_{11}T + c_{11}T \ln T$

Note this is of the same form as that of the Brokaw reference !



# Kujik Bandgap Reference

$$\frac{I_{D2}}{I_{D1}} = \text{constant}$$



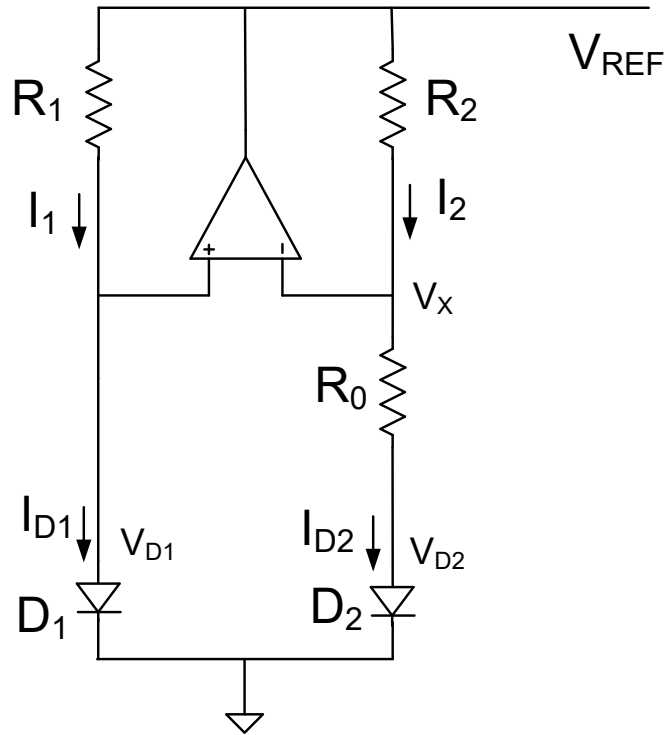
[12] K. Kujik, "A Precision Reference Voltage Source", IEEE Journal of Solid State Circuits, Vol. 8, pp. 222-226, June 1973.

# Kujik Bandgap Reference

$$I_{R0} = \frac{\Delta V_{BE}}{R_0}$$

$$I_2 = I_{R0}$$

$$V_{REF} = I_2 R_2 + V_{BE1}$$



solving, we obtain

$$V_{REF} = \frac{R_2}{R_0} \Delta V_{BE} + V_{BE1}$$

$$V_{REF} = a_{22} + b_{22}T + c_{22}T \ln T$$



<b>Brokaw</b>	<b>Banba</b>
<b>Mietus</b>	<b>Modified Banba</b>
<b>Modified Mietus</b>	<b>Modified Banba</b>

<p><b>Kuijk</b></p>	<p><b>Amema</b></p>
<p><b>Modified Kuijk</b></p>	<p><b>Zhu</b></p>

Almost all of the published bandgap references have an output of the form:

$$V_{\text{REF}} = a + bT + cT \ln T$$



	a	b	c
<u>Brokow</u>	$a_1 = V_{G0}$	$b_1 = \frac{k}{q} \left[ \frac{R_1}{R_2} \left( 1 + \frac{R_2 \alpha_1}{R_1 \alpha_2} \right) \ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left( \frac{k R_2 \alpha_1}{q R_1 \alpha_2} \frac{\ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{J_{SX} R_2} \right) \right]$	$c_1 = \frac{k}{q} (1-m)$
<u>Banba</u>	$a_2 = \left[ \frac{R_4 \theta K_3}{R_1} \right] V_{G0}$	$b_2 = \left[ \frac{k \theta K_3}{q} \right] \left[ \frac{R_4}{R_0} \ln \left( \frac{A_{D2}}{A_{D1}} \right) + \frac{R_4}{R_1} \ln \left( \frac{k}{q} \frac{\ln \left( \frac{A_{D2}}{A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX1}} \right) \right]$	$c_2 = \left[ \frac{R_4 \theta K_3}{R_1} \right] \frac{k}{q} (1-m)$
<u>Mieteus</u>	$a_3 = K_5 V_{G0}$	$b_3 = \frac{k}{q} \left[ K_3 \frac{R_4}{R_0} \ln \left( K_1 \frac{A_{D2}}{A_{D1}} \right) + K_5 \left[ \ln \frac{k}{q} + \frac{\ln \left( K_1 \frac{A_{D2}}{A_{D1}} \right)}{J_{SX} A_{D2}} \right] \right]$	$c_3 = \frac{k}{q} K_5 (1-m)$
<u>Kuijk</u>	$a_4 = V_{G0}$	$b_4 = \frac{k}{q} \left[ \frac{R_2}{R_0} \ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left( \frac{R_2}{R_1} \frac{k}{q} \frac{\ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX}} \right) \right]$	$c_4 = \frac{k}{q} (1-m)$
Modified Kuijk	$a_5 = V_{G0}$	$b_5 = \frac{k}{q} \left[ \frac{R_2}{R_0} \ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left( \frac{R_2}{R_1} \frac{k}{q} \frac{\ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX}} \right) \right]$	$c_5 = \frac{k}{q} (1-m)$
Modified Kuijk	$a_6 = K V_{G0}$	$b_6 = \frac{k}{q} K \left[ \frac{R_2}{R_0} \ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \ln \left( \frac{R_2}{R_1} \frac{k}{q} \frac{\ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right)}{R_0 A_{D1} \tilde{J}_{SX}} \right) \right]$	$c_6 = \frac{k}{q} K (1-m)$
<u>Doyle</u>	$a_6 = V_{G0}$	$b_6 = \frac{k}{q} \left[ \frac{K_1}{R_1} \frac{R_2}{R_0} \ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right) + \frac{R_2 + R_3}{R_1 + R_2 + R_3} \ln \left( \frac{K_1 k}{R_1 q} \ln \left( \frac{R_2 A_{D2}}{R_1 A_{D1}} \right) \right) - \ln(J_{SX} A_{D2}) \right]$	$c_6 = \frac{k}{q} \left( \frac{R_2 + R_3}{R_1 + R_2 + R_3} - m \right)$

$$V_{\text{REF}} = a + bT + cT \ln T$$

- Start-up Circuits Required on all Bandgap References discussed here
- Bandgap circuits widely used to build voltage references for over 4 decades
- Basic bandgap circuits still used today
- Trimming often required to set inflection point at desired temperature
- Offset voltage of Op Amp and TCR of resistors degrade performance
- Experimental performance often a factor of 2 to 10 worse than that predicted here but still quite good
- Ongoing research activities focusing on improving performance of bandgap references



Stay Safe and Stay Healthy !

End of Lecture 41